

# Mitigating Parameter Variation with Dynamic Fine-Grain Body Biasing

**Radu Teodorescu, Jun Nakano, Abhishek Tiwari  
and Josep Torrellas**

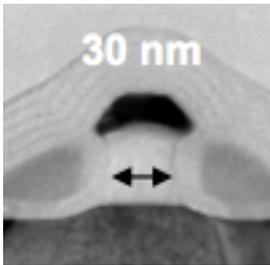
University of Illinois at Urbana-Champaign  
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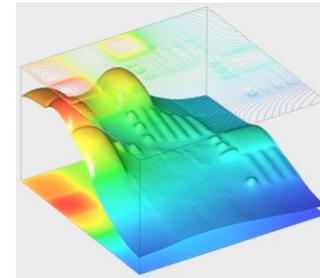


# Parameter variation: roadblock to scaling

## Process Variation



## Temperature Variation

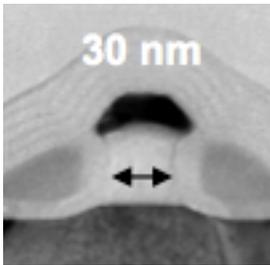


## Supply Voltage Variation

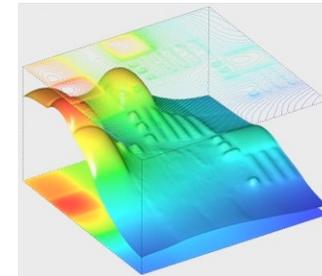


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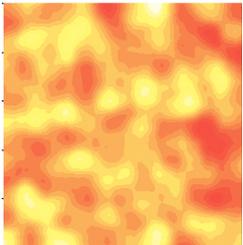
## Process Variation



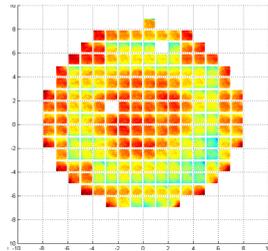
## Temperature Variation



Within die (WID)

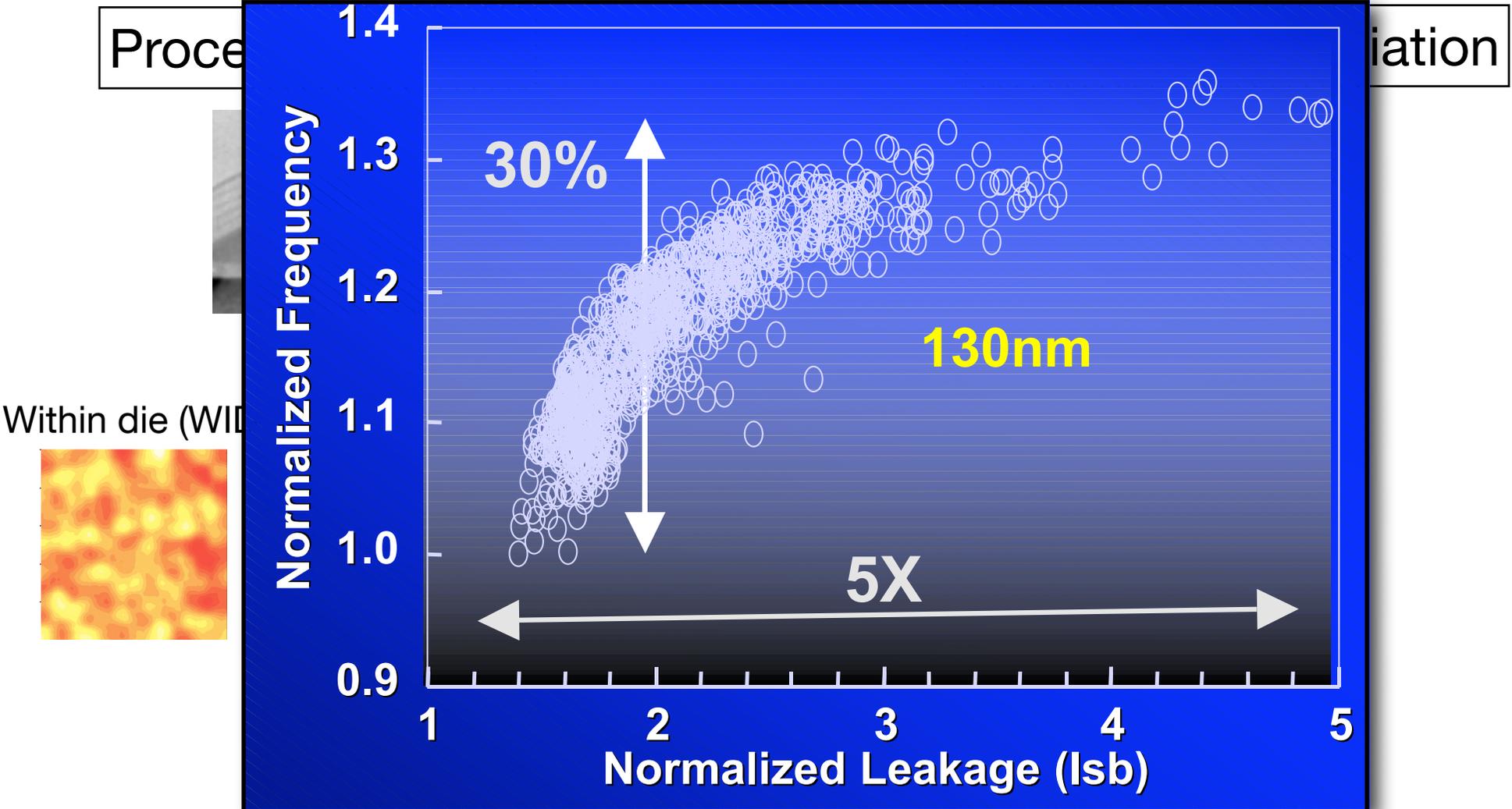


Die-to-die (D2D)





# Parameter variation: roadblock to scaling

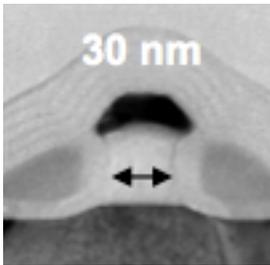


[Shekhar Borkar, Intel Corp.]

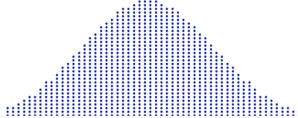
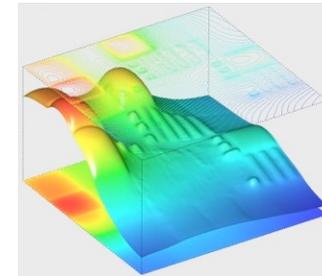


# Technology scaling faces a major roadblock

Process Variation



Temperature Variation



Threshold Voltage ( $V_{th}$ )

Chip frequency



Chip leakage power





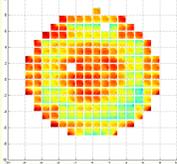
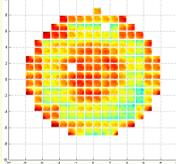
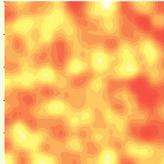
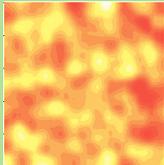
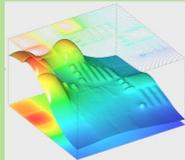
# Body biasing

- Well known technique for  $V_{th}$  control
- A voltage is applied between source/drain and substrate of a transistor
- Forward body bias (FBB)  $V_{th}$  ↓ Freq ↑ Leak ↑
- Reverse body bias (RBB)  $V_{th}$  ↑ Freq ↓ Leak ↓
- Key knob to trade off frequency for leakage



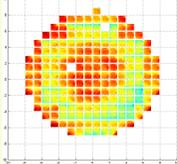
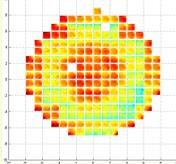
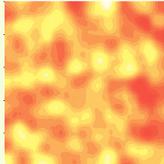
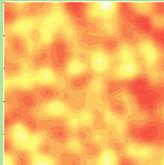
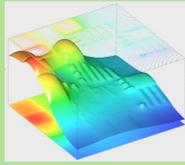


# Body bias design space

Time \ Space	Static	Dynamic
Chip-wide	 D2D $V_{th}$ Variation [Intel Xscale] [Intel's 80-core chip]	 D2D $V_{th}$ Variation T Variation
Fine-grain	 WID $V_{th}$ Variation [Tschanz et al]	 WID $V_{th}$ Variation T Variation (space and time) 



# Body bias design space

Time \ Space	Static	Dynamic
Chip-wide	 <p>D2D <math>V_{th}</math> Variation [Intel Xscale] [Intel's 80-core chip]</p>	 <p>D2D <math>V_{th}</math> Variation T Variation</p>
Fine-grain	 <p>WID <math>V_{th}</math> Variation <b>S-FGBB</b> [Tschanz et al]</p>	 <p>WID <math>V_{th}</math> Variation <b>D-FGBB</b> (space and time)</p> 



# Outline

- Background on S-FGBB
- Dynamic fine-grain body biasing (D-FGBB)
- Environments
- Evaluation
- Conclusions



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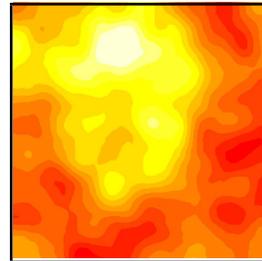
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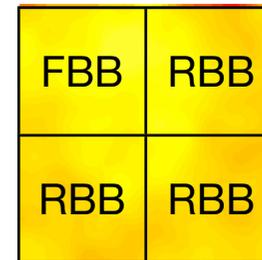
# Static fine-grain body biasing

[Tschanz et al, ISSCC 2002]

$V_{th}$  variation



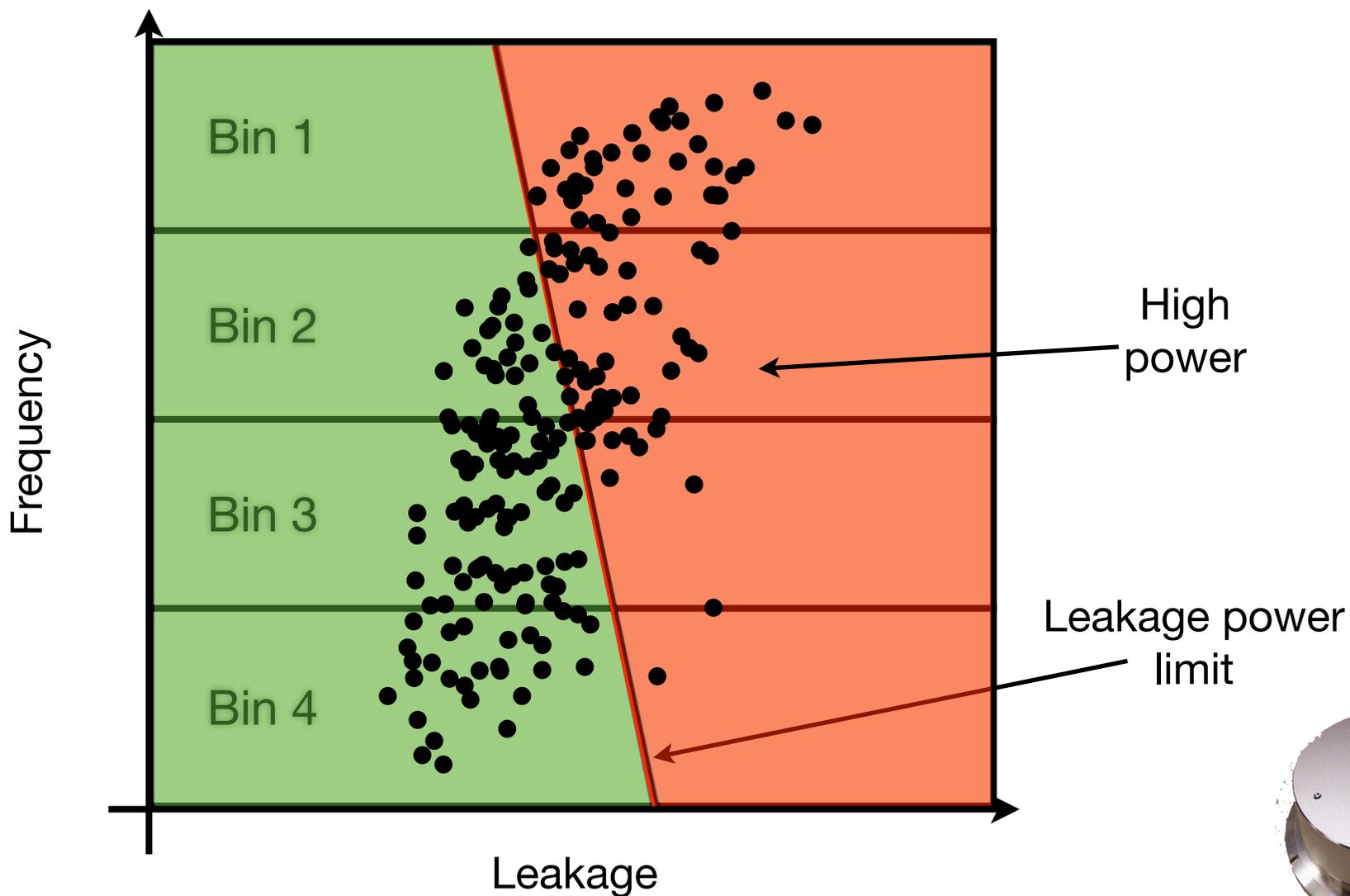
Fine Grain Body Bias



- The chip is divided in BB cells
  - Slow cells receive FBB - increase speed
  - Leaky cells receive RBB - save leakage
- The result is reduced WID variation (delay, power)
- BB voltages determined at manufacturing
- Fixed for the lifetime of the chip

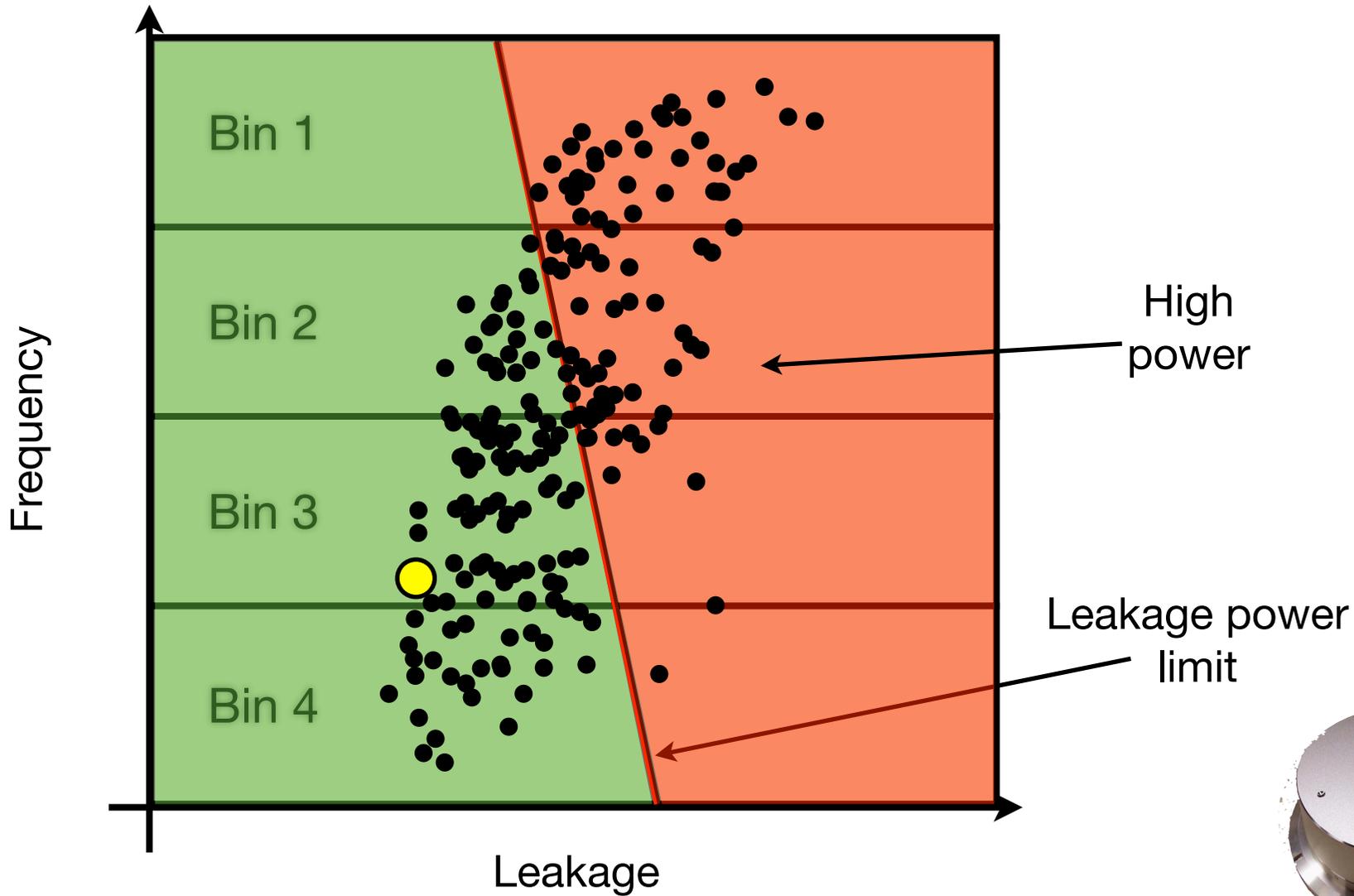


# Frequency binning



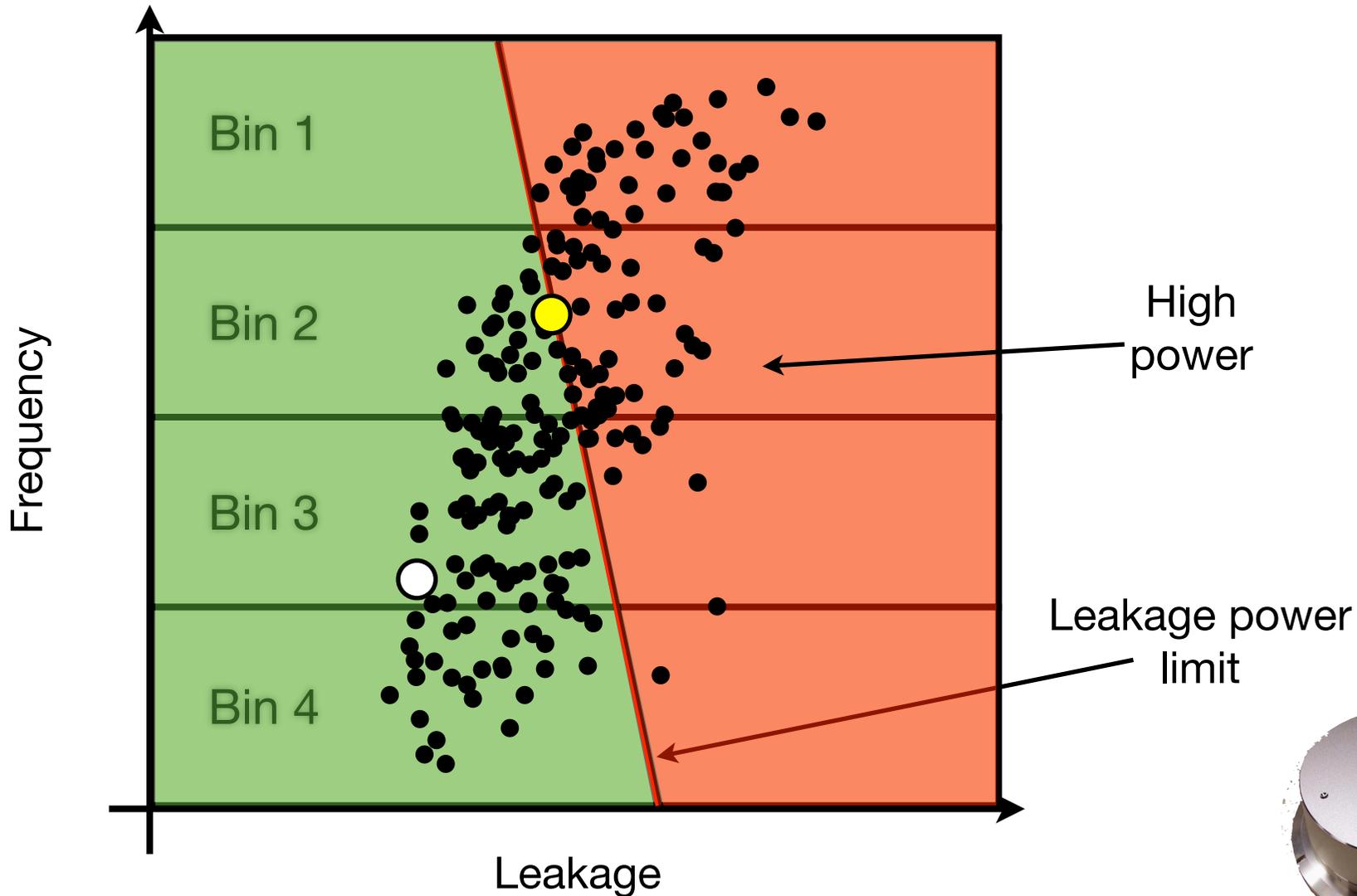


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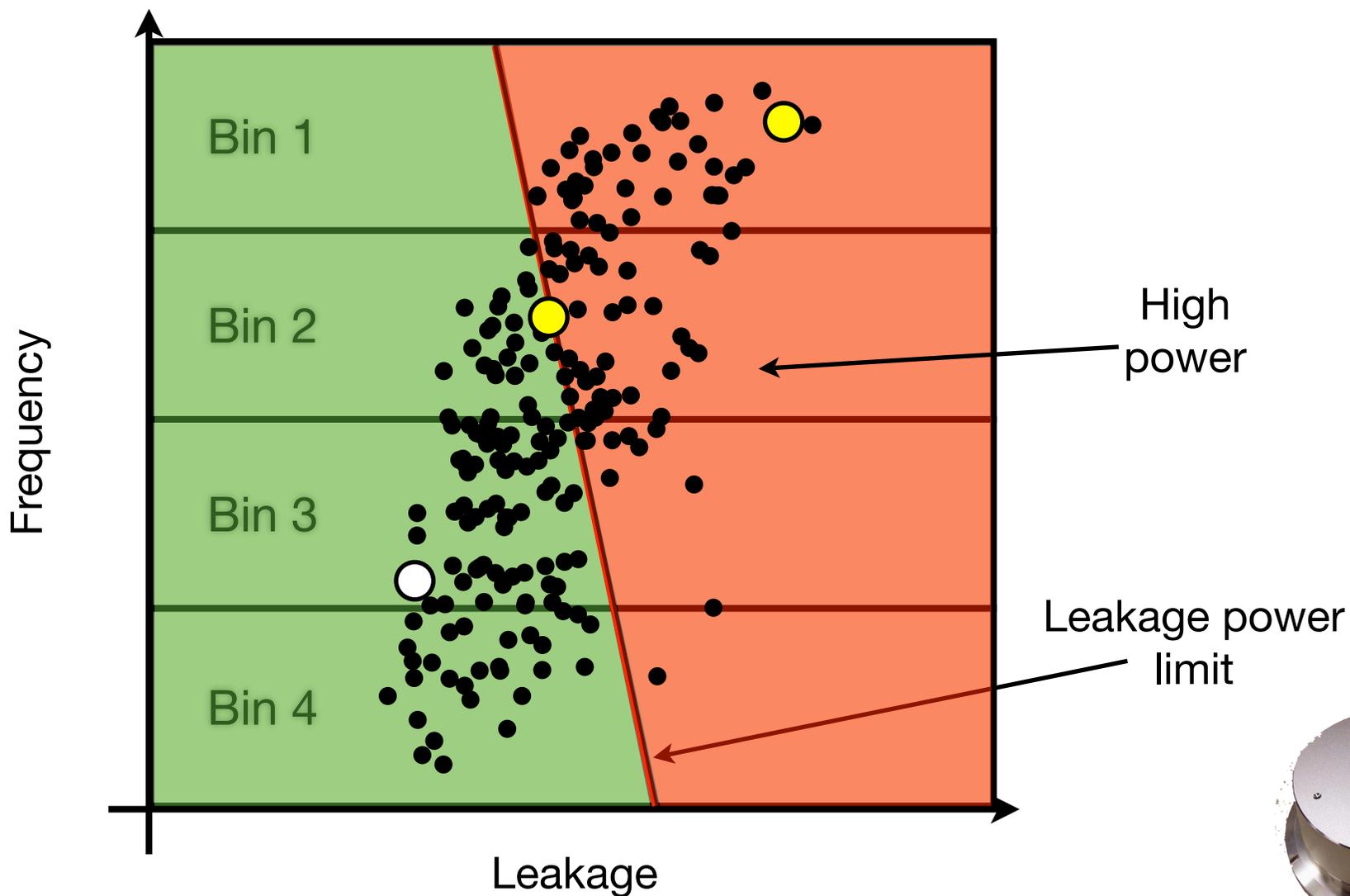


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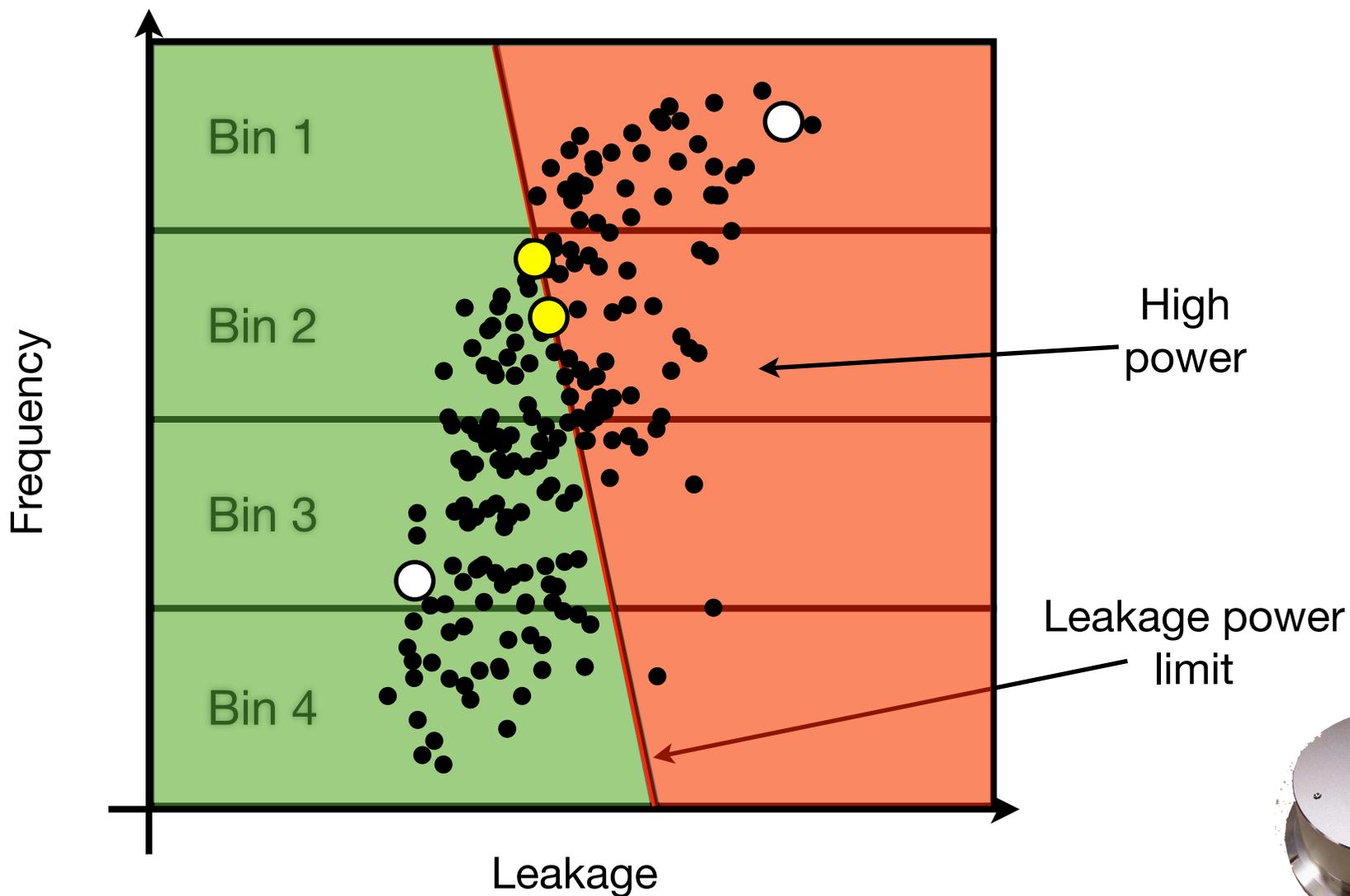


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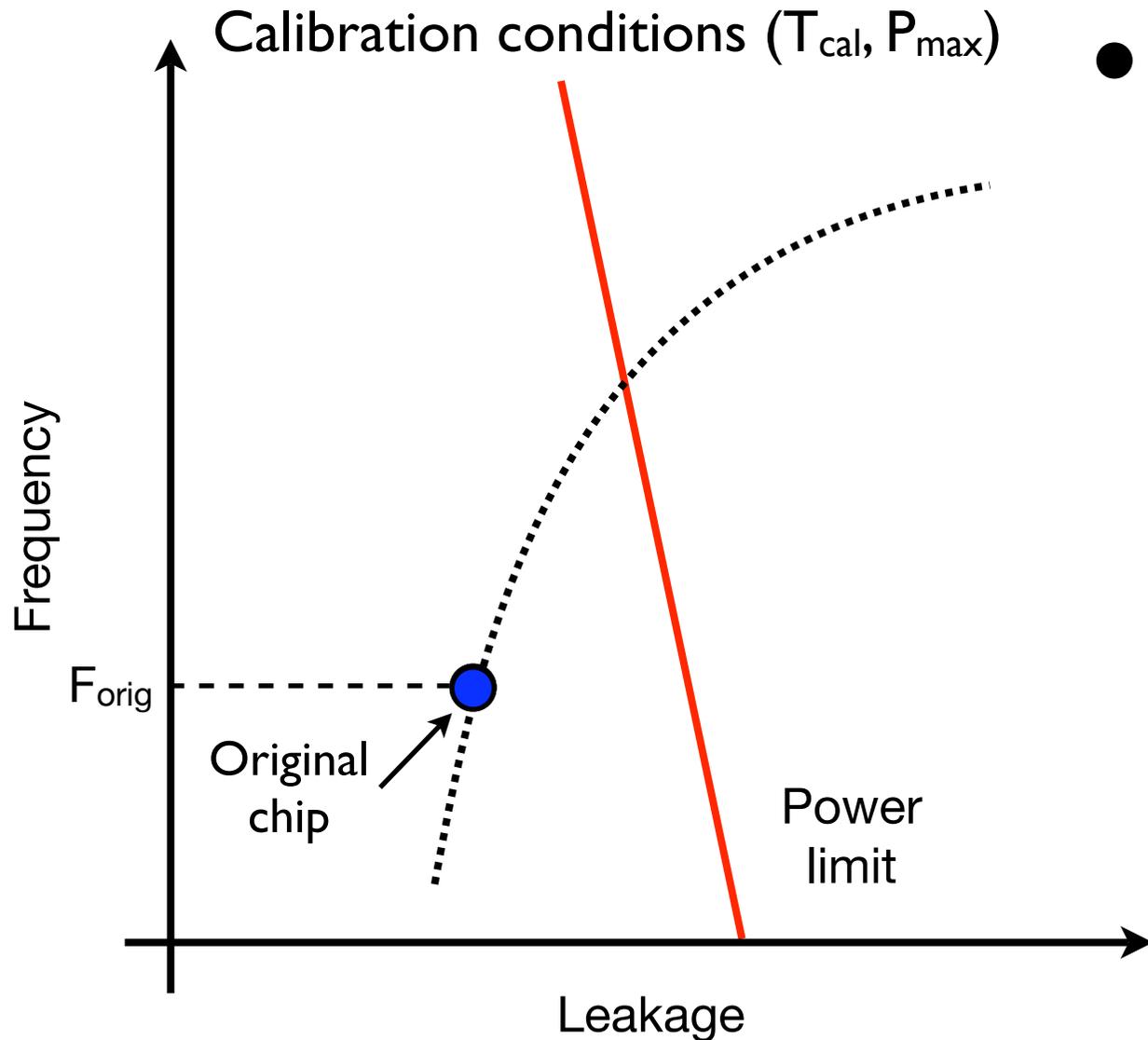


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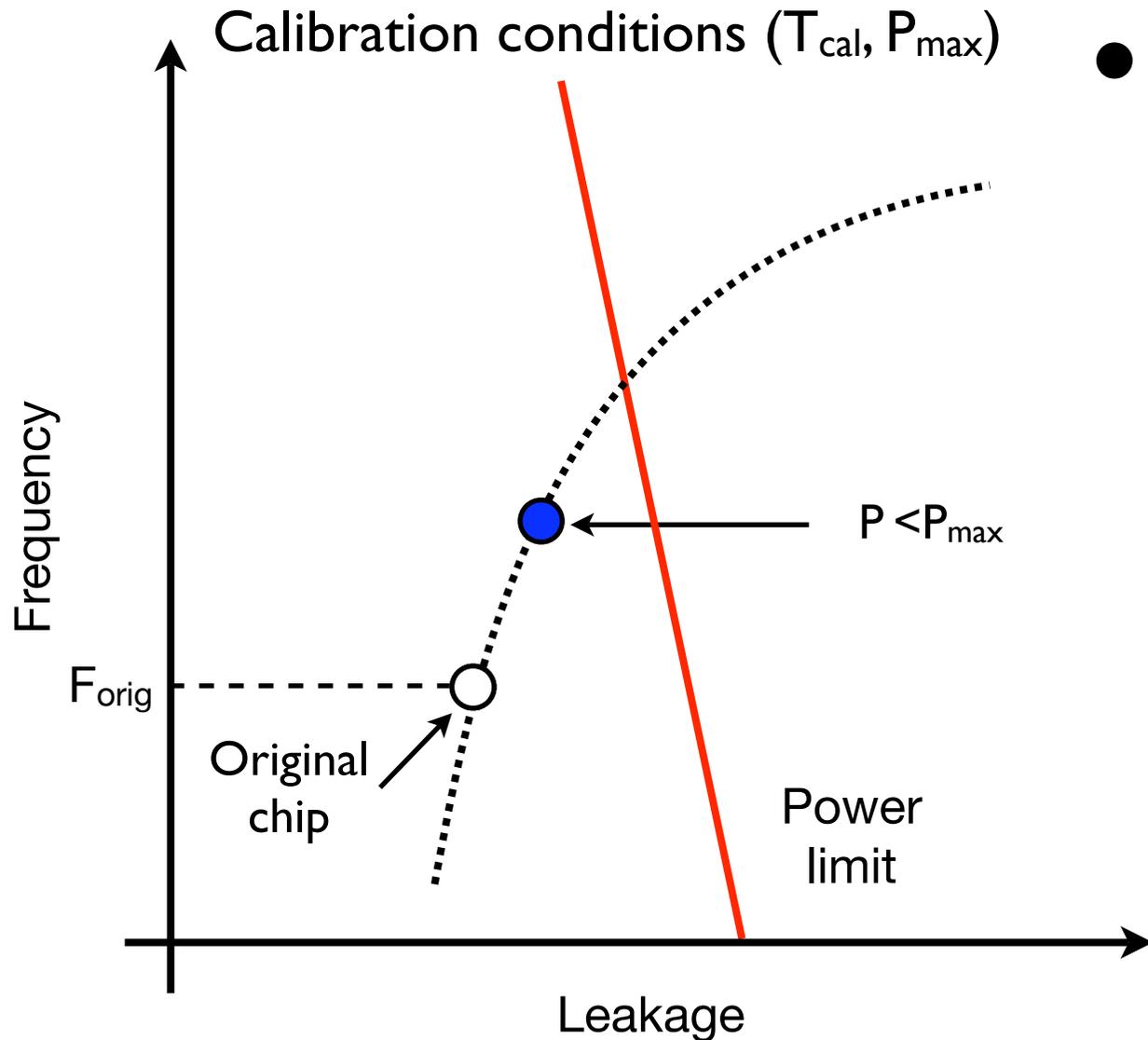
# Calibration after manufacturing



- Calibration takes place at maximum temperature  $T_{cal}$  (burn-in oven)



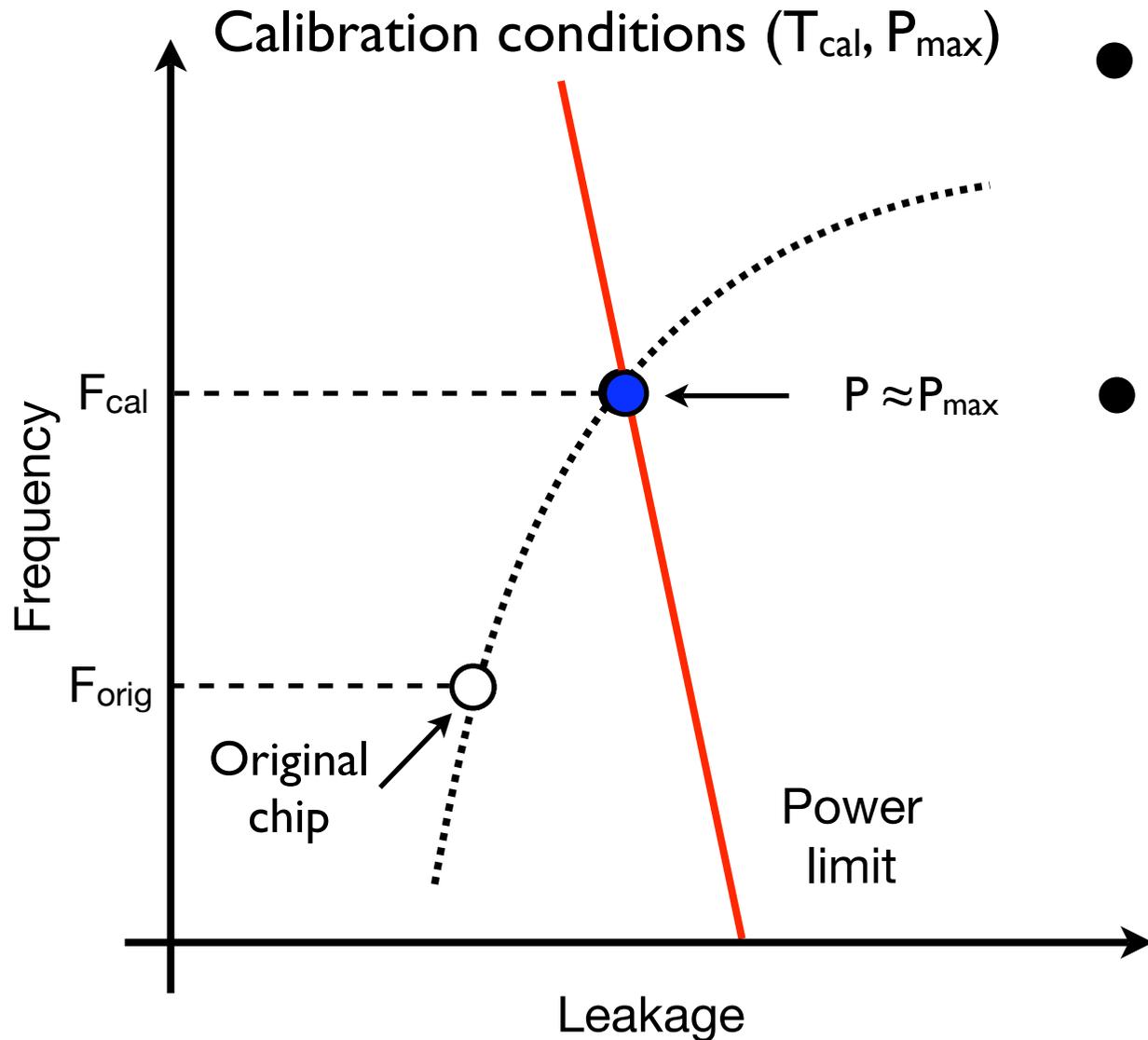
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# Calibration after manufacturing



- Calibration takes place at maximum temperature  $T_{cal}$  (burn-in oven)
- $F_{cal}$  becomes the chip's frequency



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# Motivation for D-FGBB

- Significant temperature variation:
  - Space: across different functional units, on chip
  - Time: as the activity factor of the workload changes
  - Between average and worst case conditions ( $T_{cal}$ )
- D-FGBB can exploit this temperature variation
  - Adapt the body bias to changing conditions



# Motivation for D-FGGB

- **Optimal** body bias:

The body bias than **minimizes** leakage power at the target frequency

- Circuit delay changes with temperature

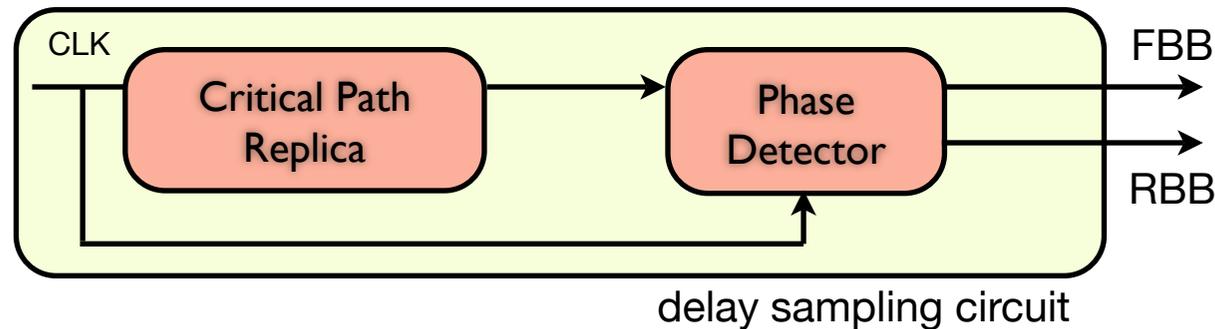
- Therefore optimal BB changes with temperature

The goal of D-FGGB is to keep the body bias optimal as T changes



# Finding the optimal BB

- Measure the delay of each BB domain (cell)
- Delay sampling circuit:

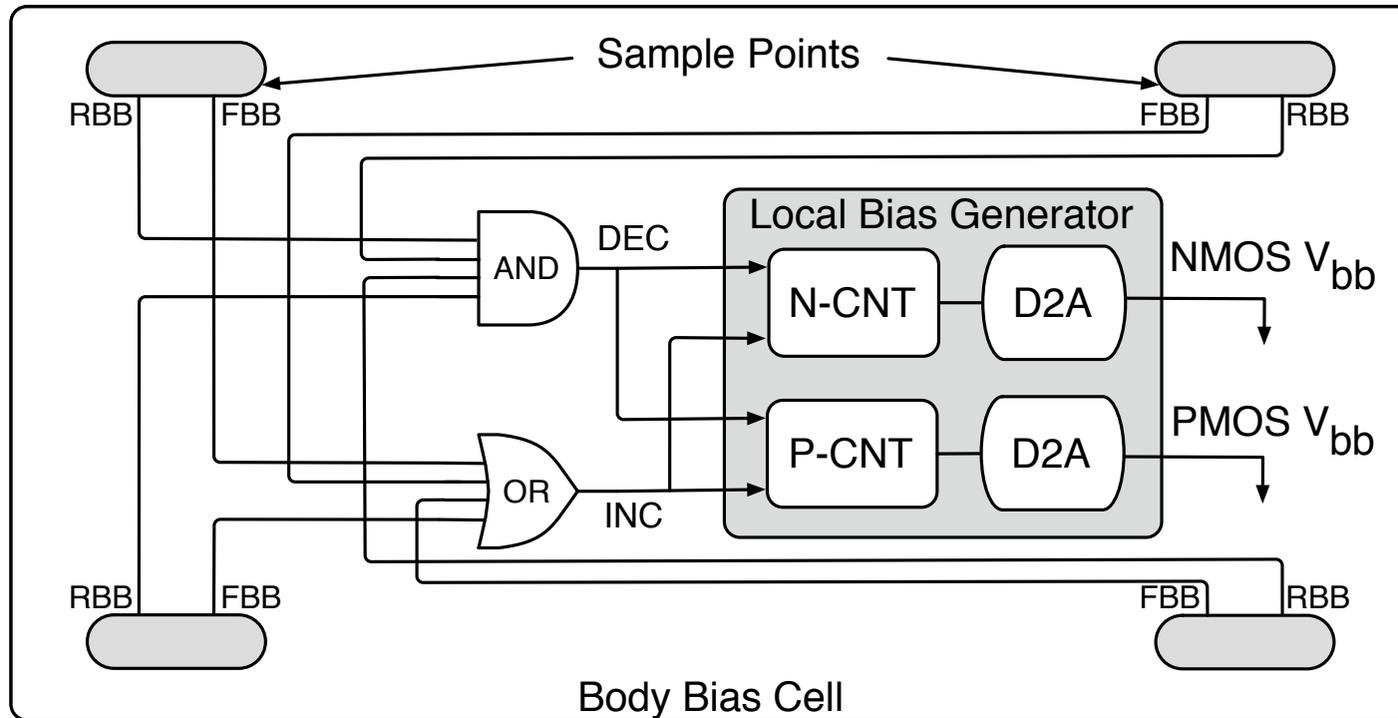


- Phase detector - measures delay of critical path replica
  - If slow - FBB signal raised
  - If fast - RBB signal raised



# Applying dynamic fine-grain BB

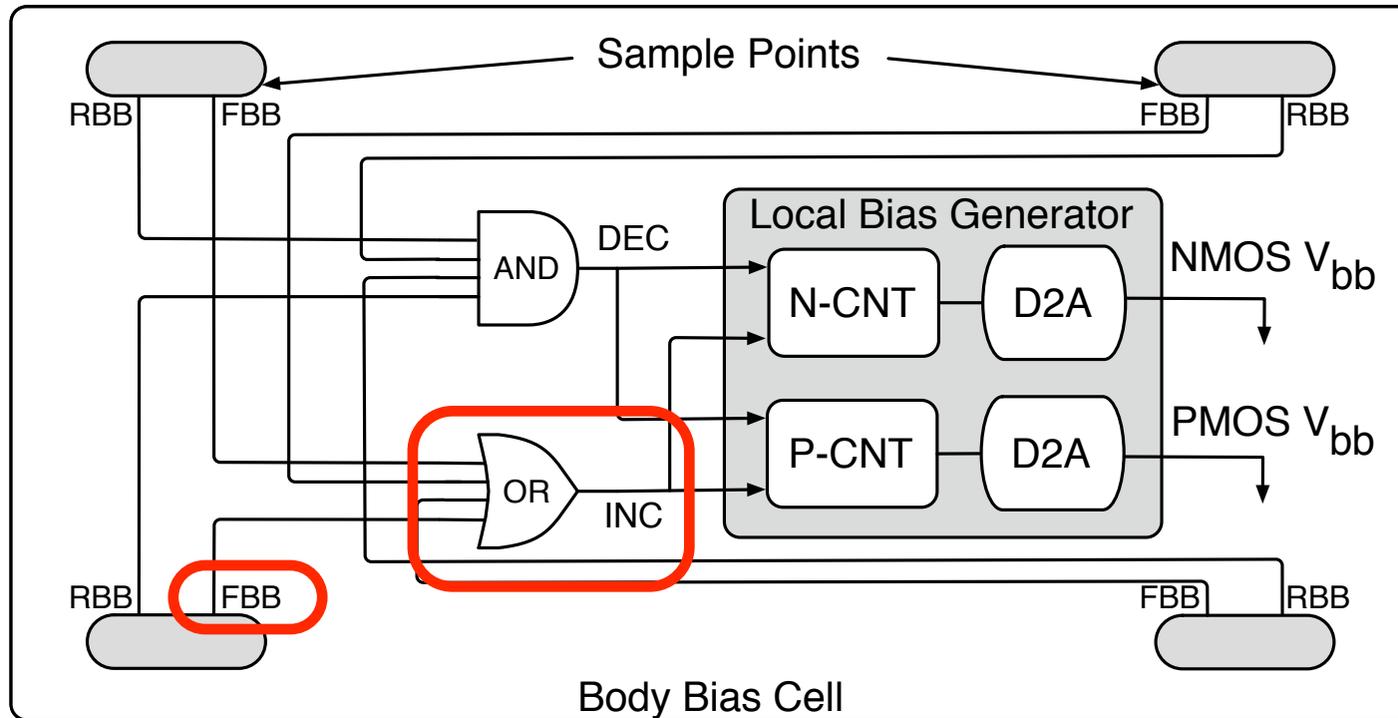
- BB is determined based on feedback from delay samples





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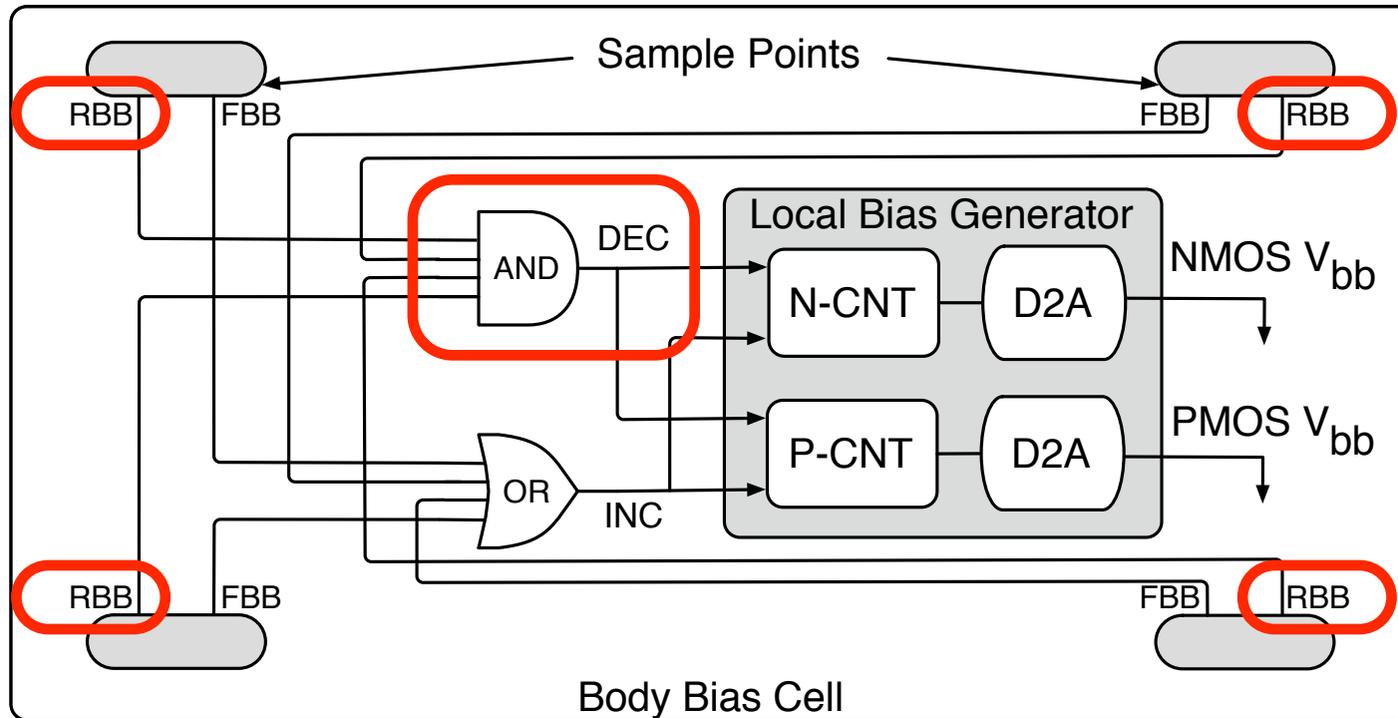






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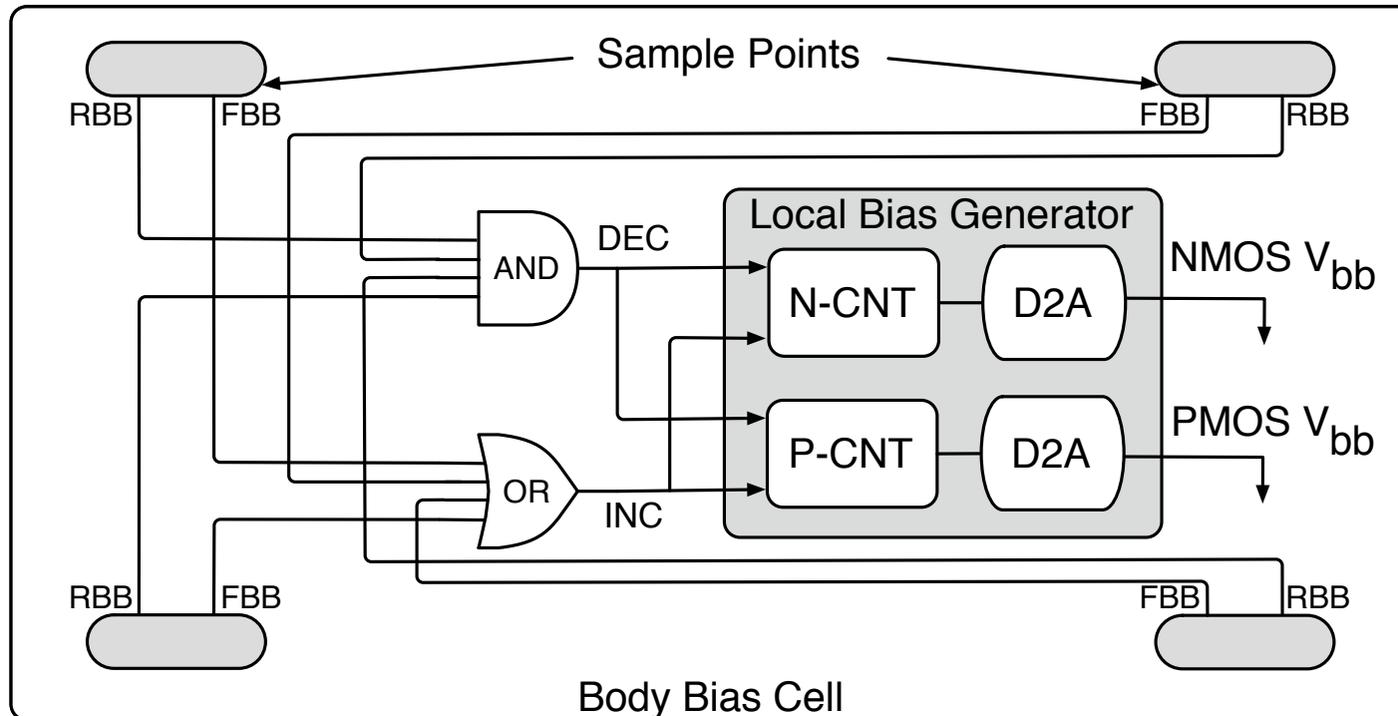
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# Applying dynamic fine-grain BB

- BB is determined based on feedback from delay samples



- The BB changes until optimal delay is reached
- BB stays constant, until T conditions change again



# Outline

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# D-FGGB environments

Operating environments	D-FGGB
Standard 	Minimize <b>leakage power</b> at $F_{cal}$
High performance 	Maximize <b>average frequency</b>
Low Power 	Minimize <b>leakage power</b> at $F_{orig}$

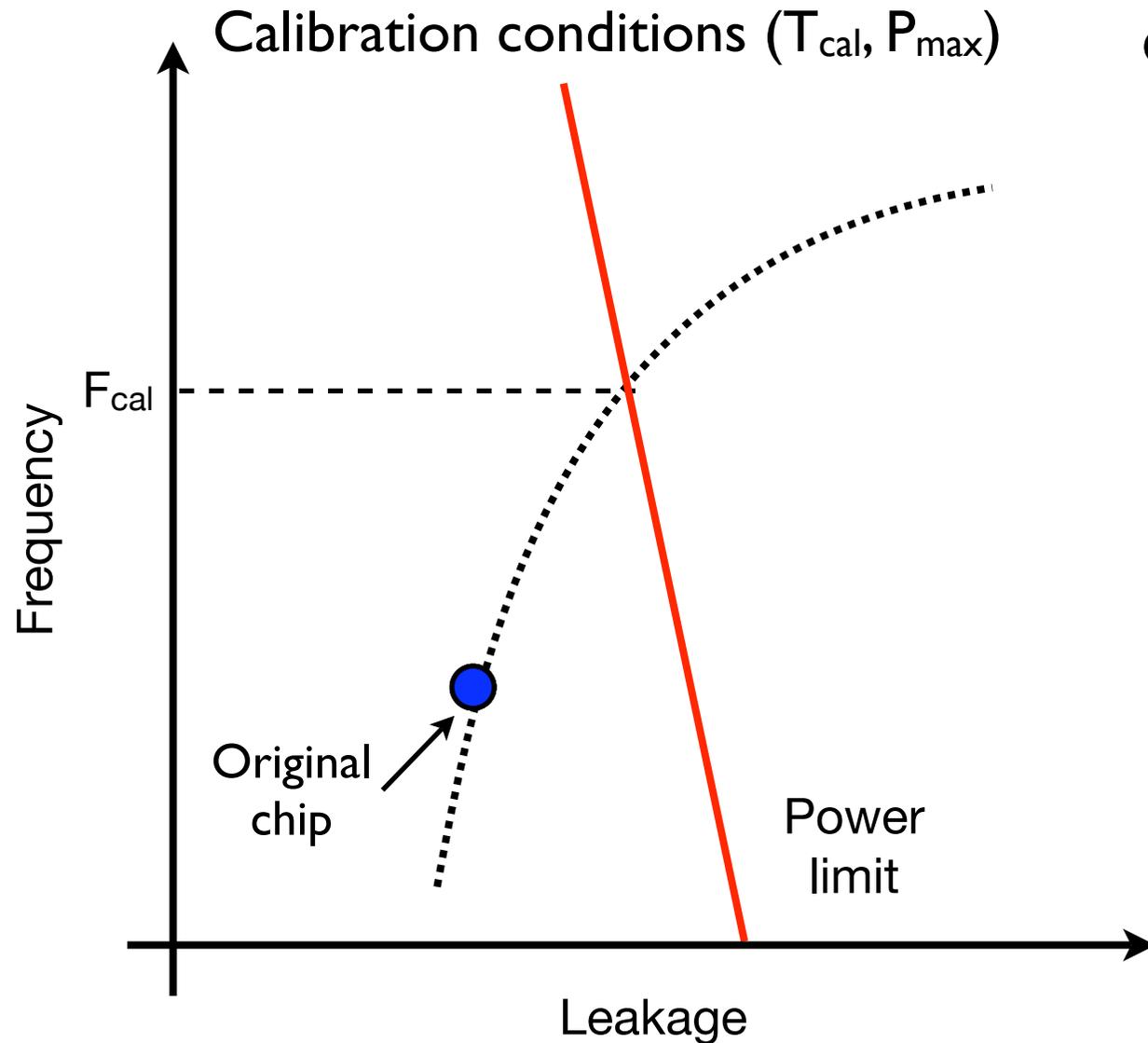


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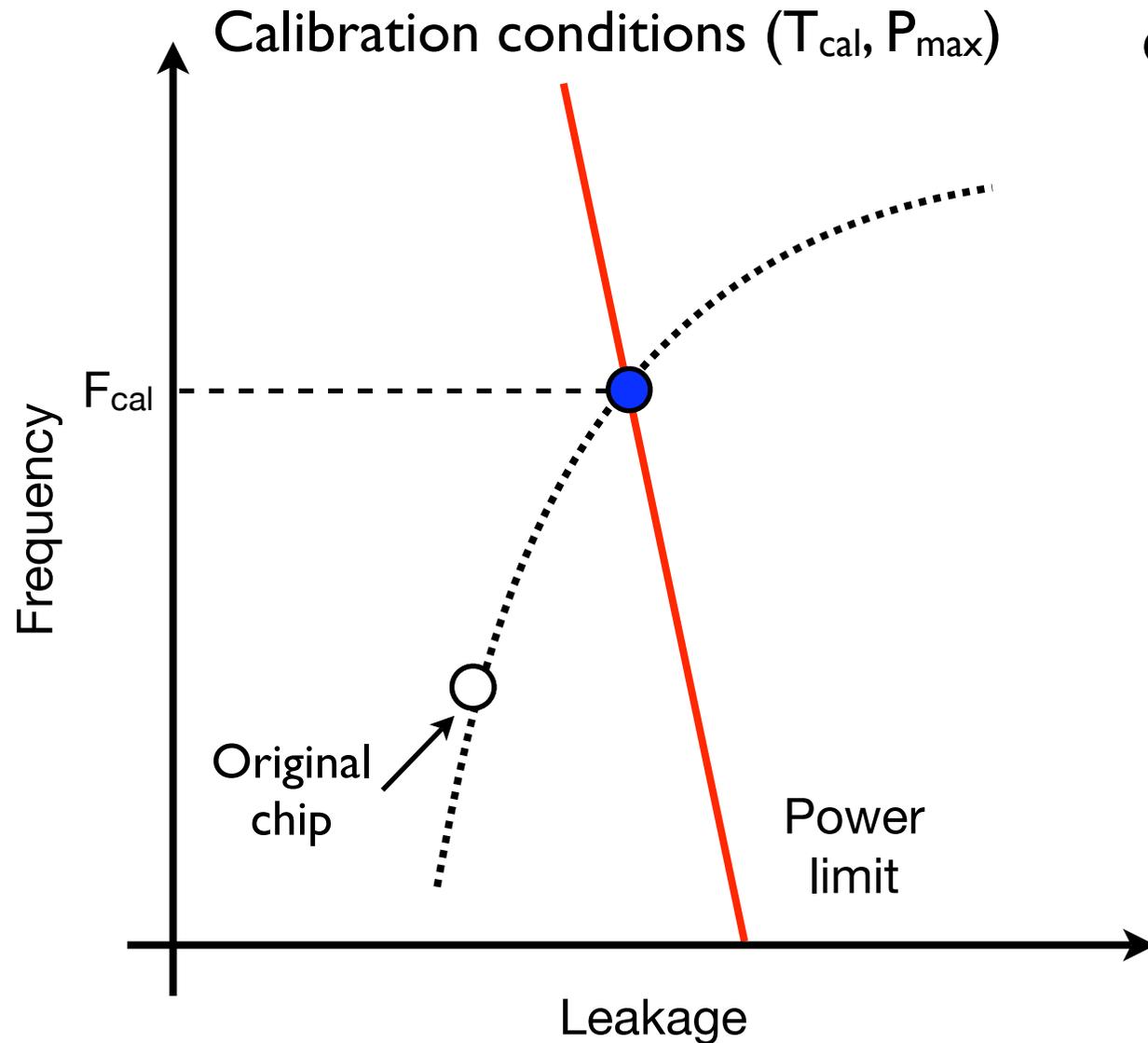
# Standard environment



- S-FGGB finds and sets  $F_{cal}$



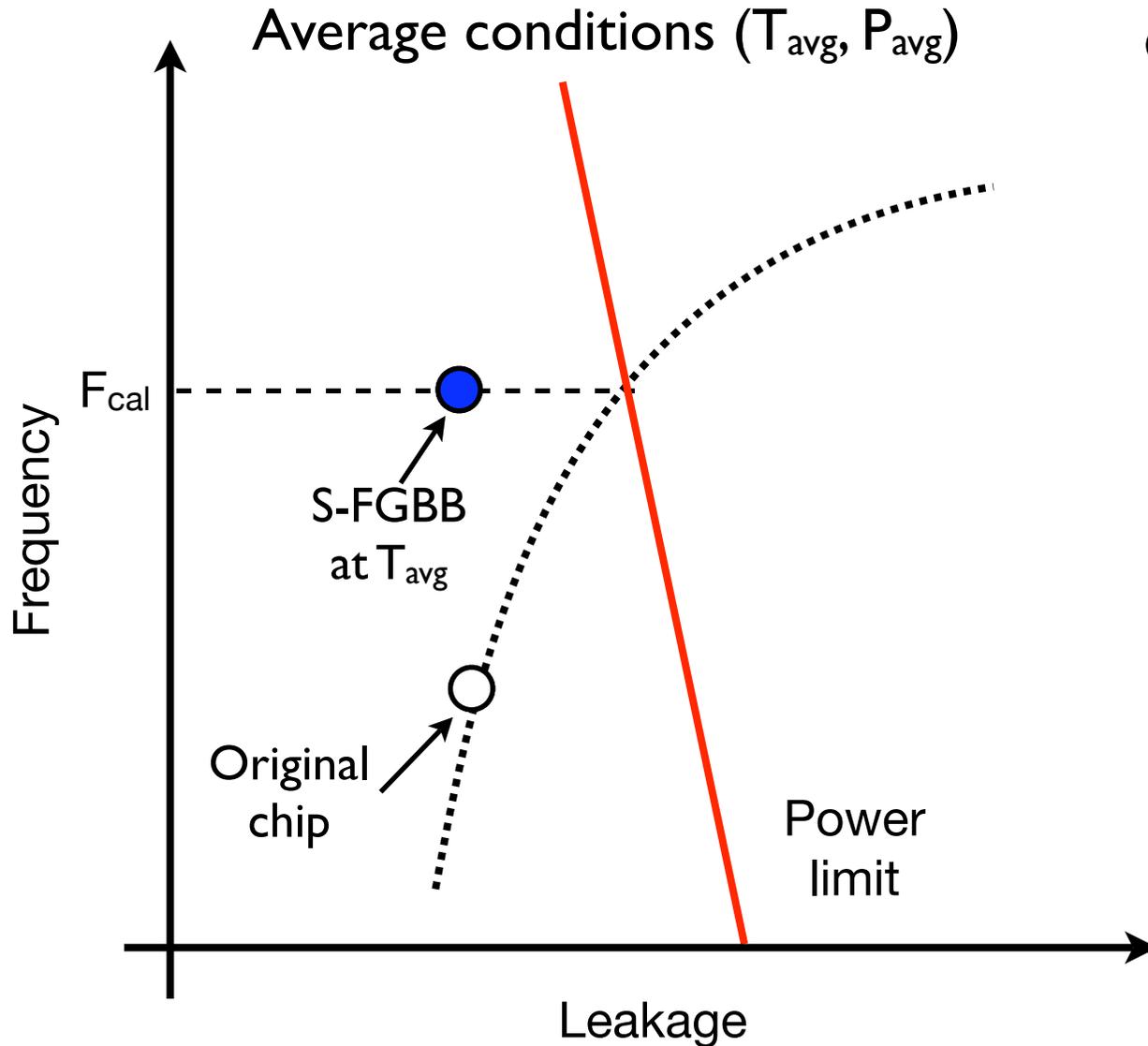
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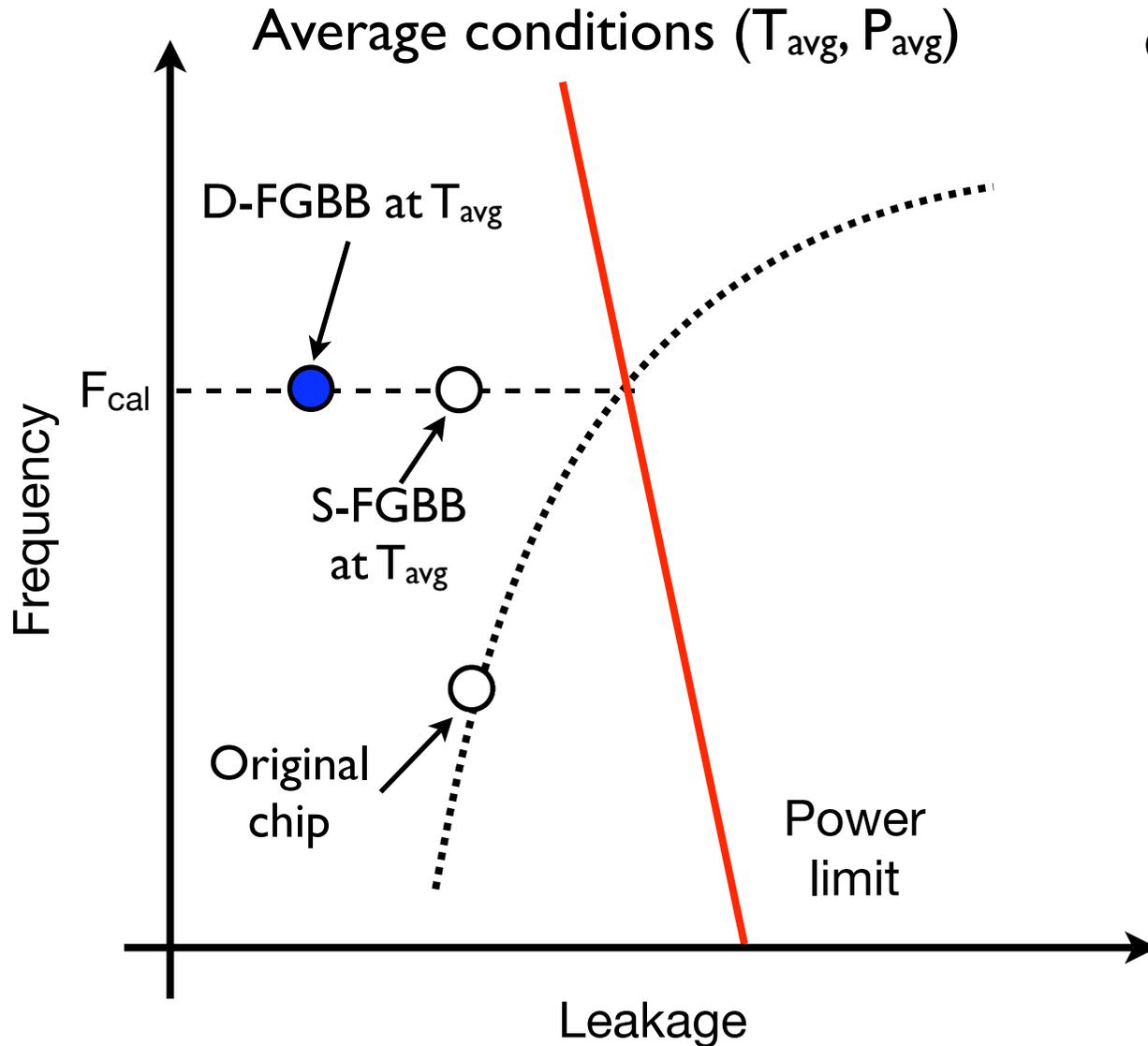
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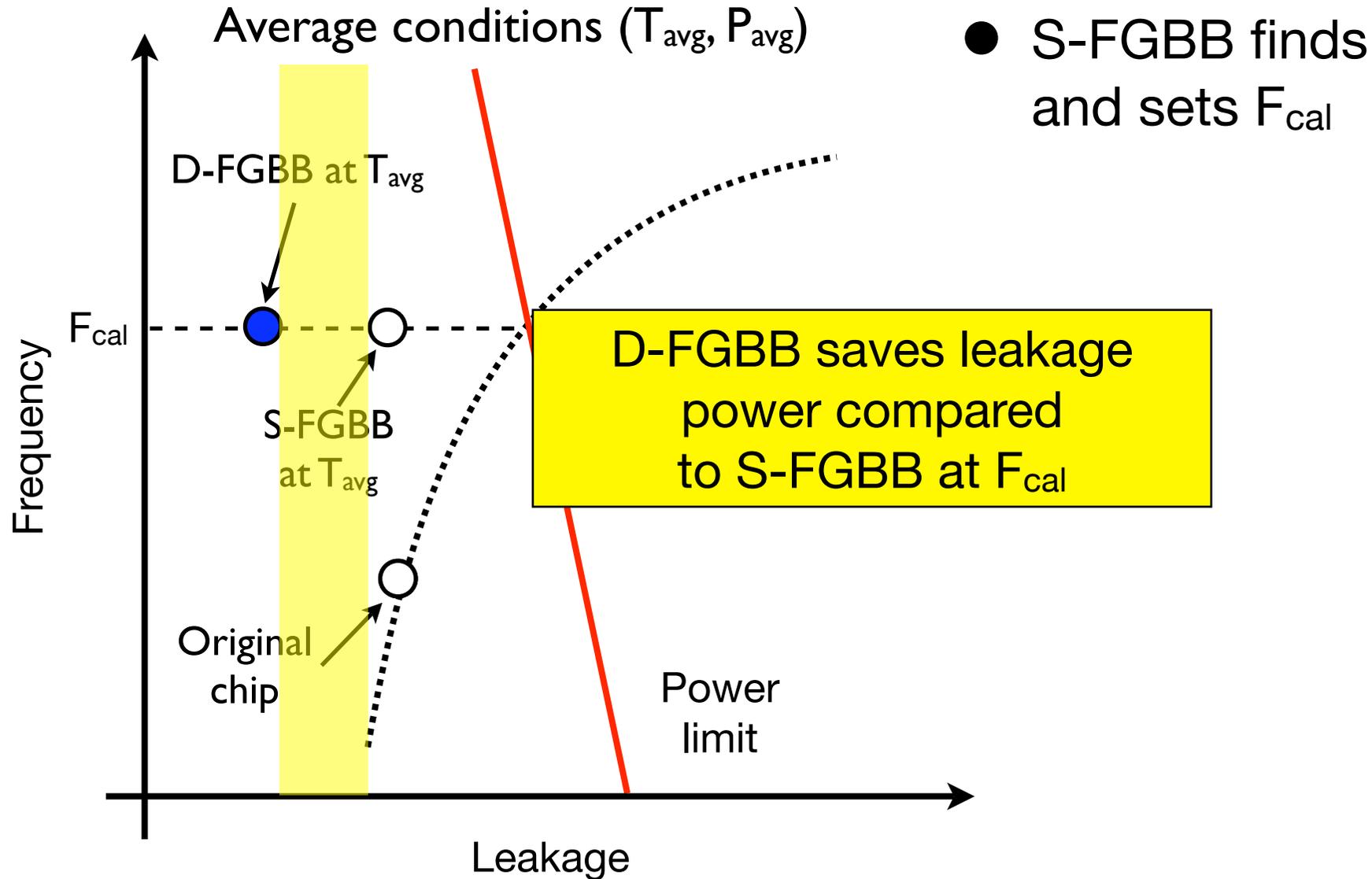
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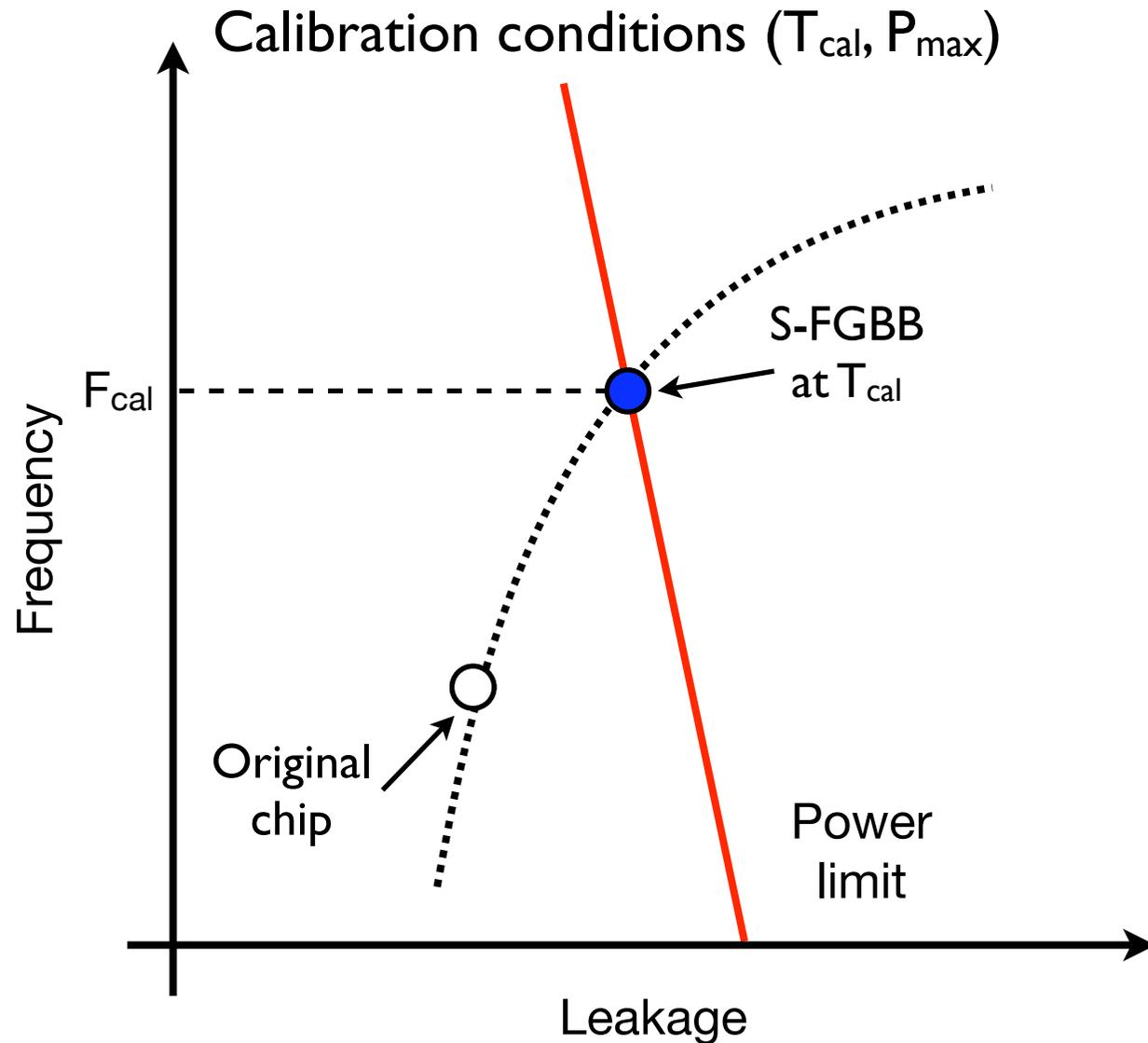


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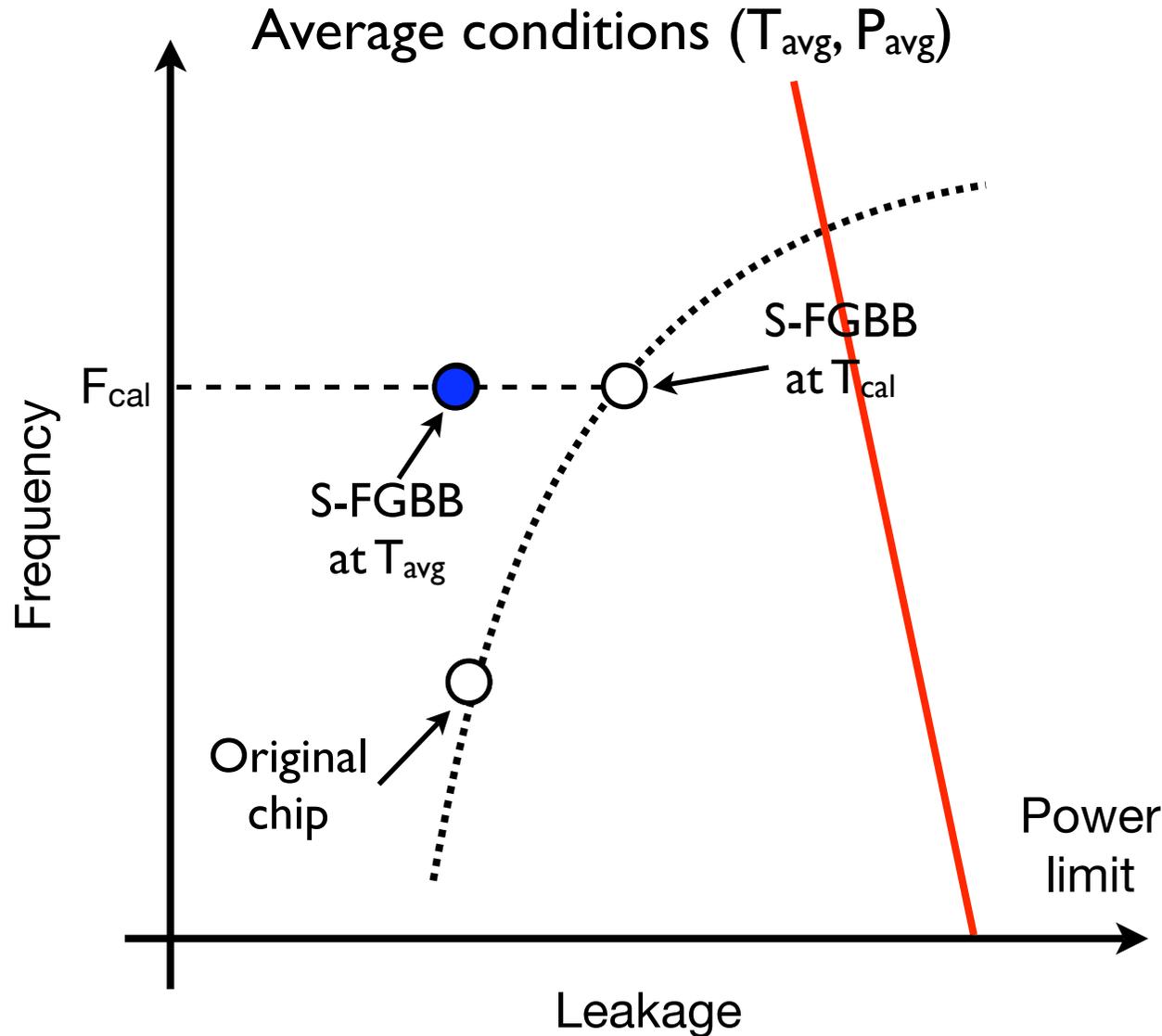
# High performance



- Average power  $P_{avg} \ll P_{max}$



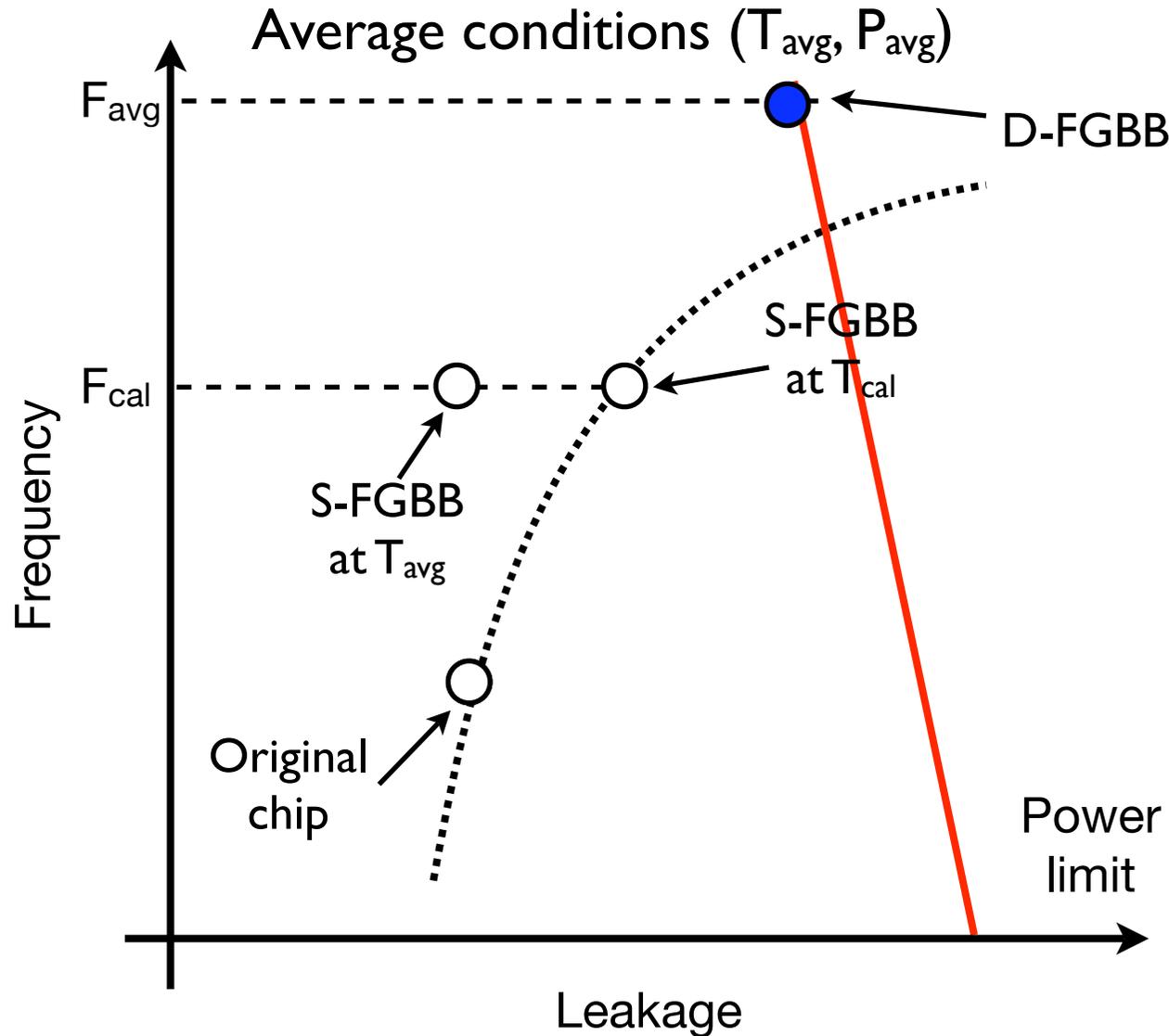
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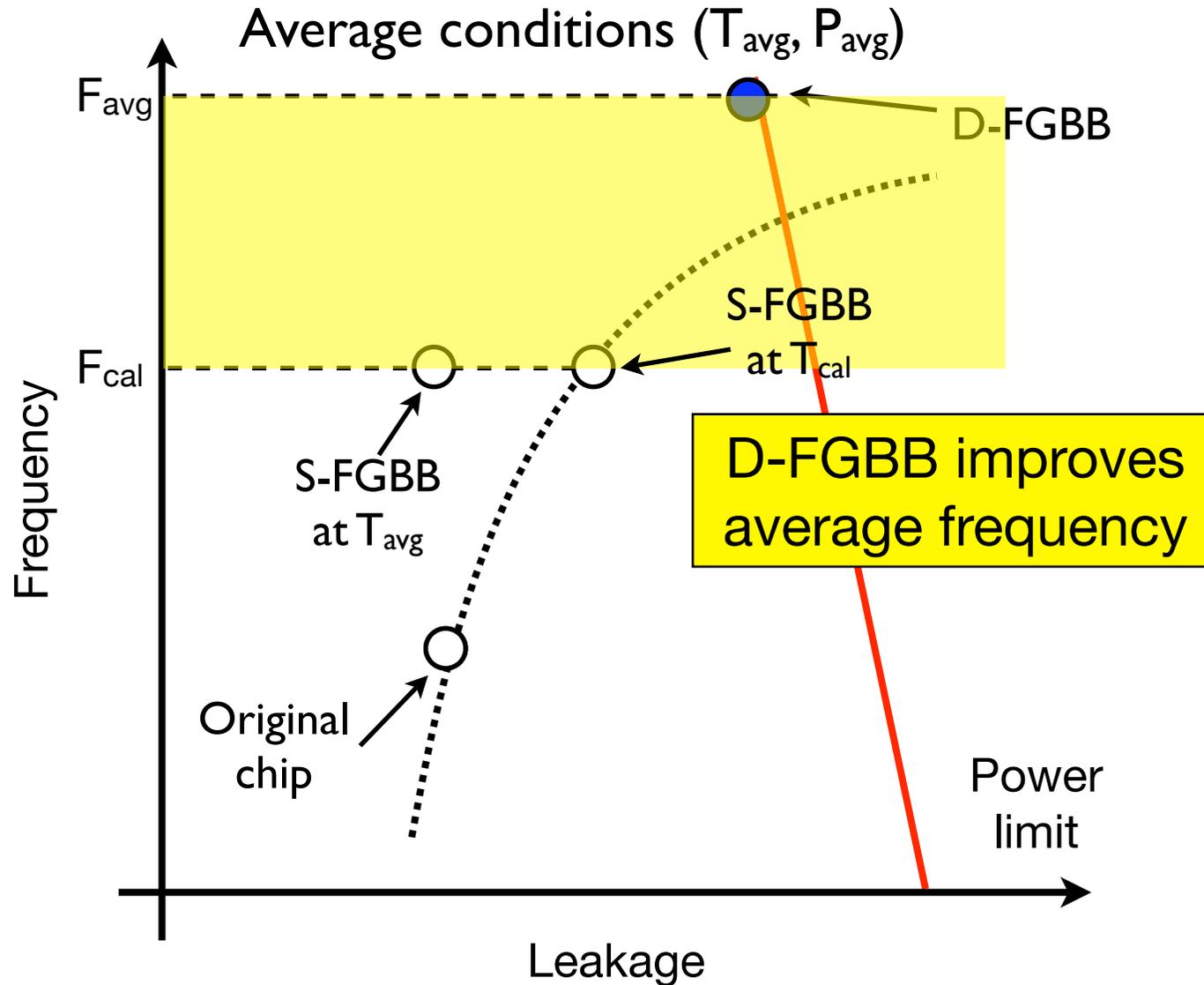
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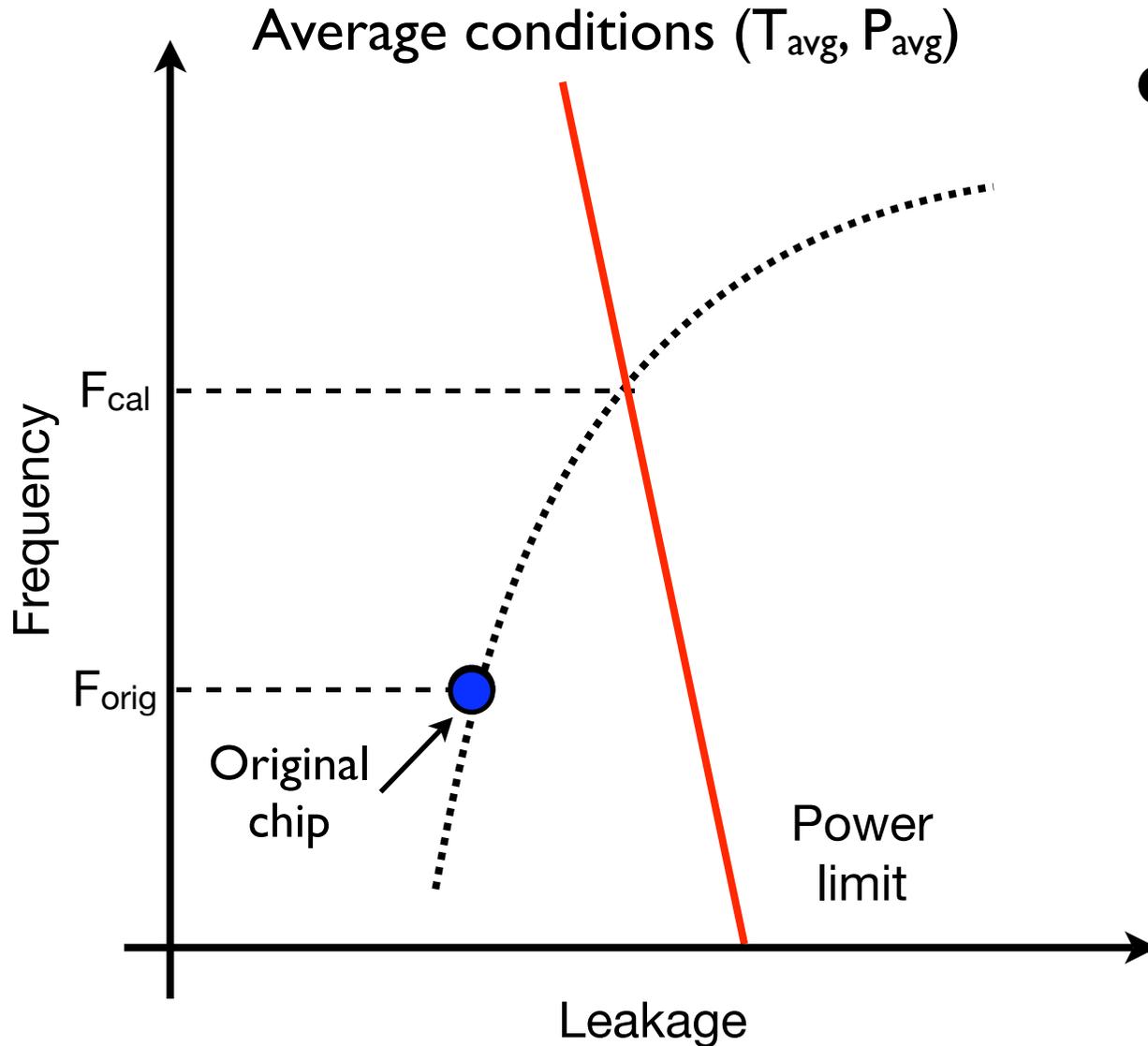


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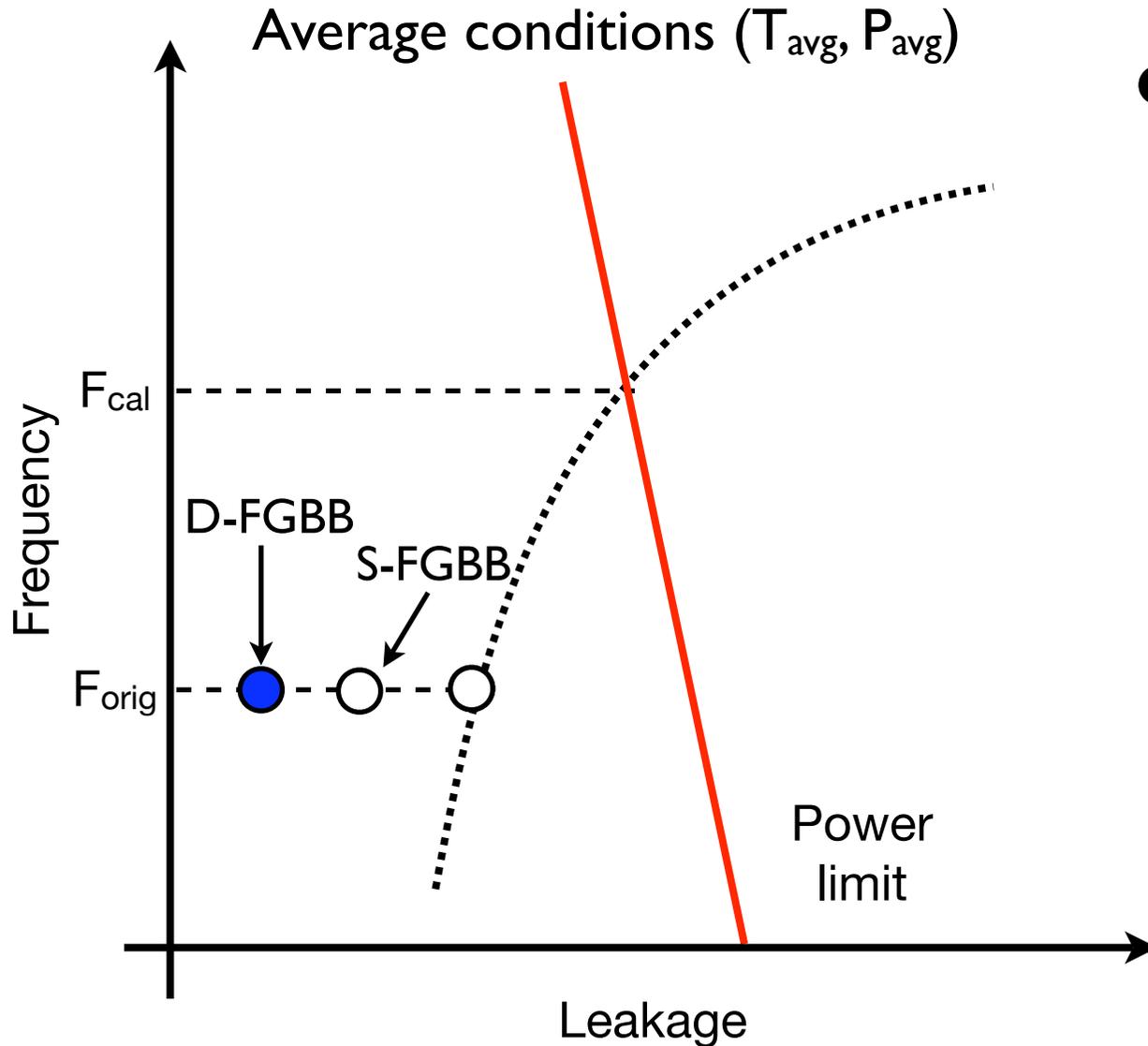
# Low power



- The chip runs at its original frequency ( $F_{orig}$ )



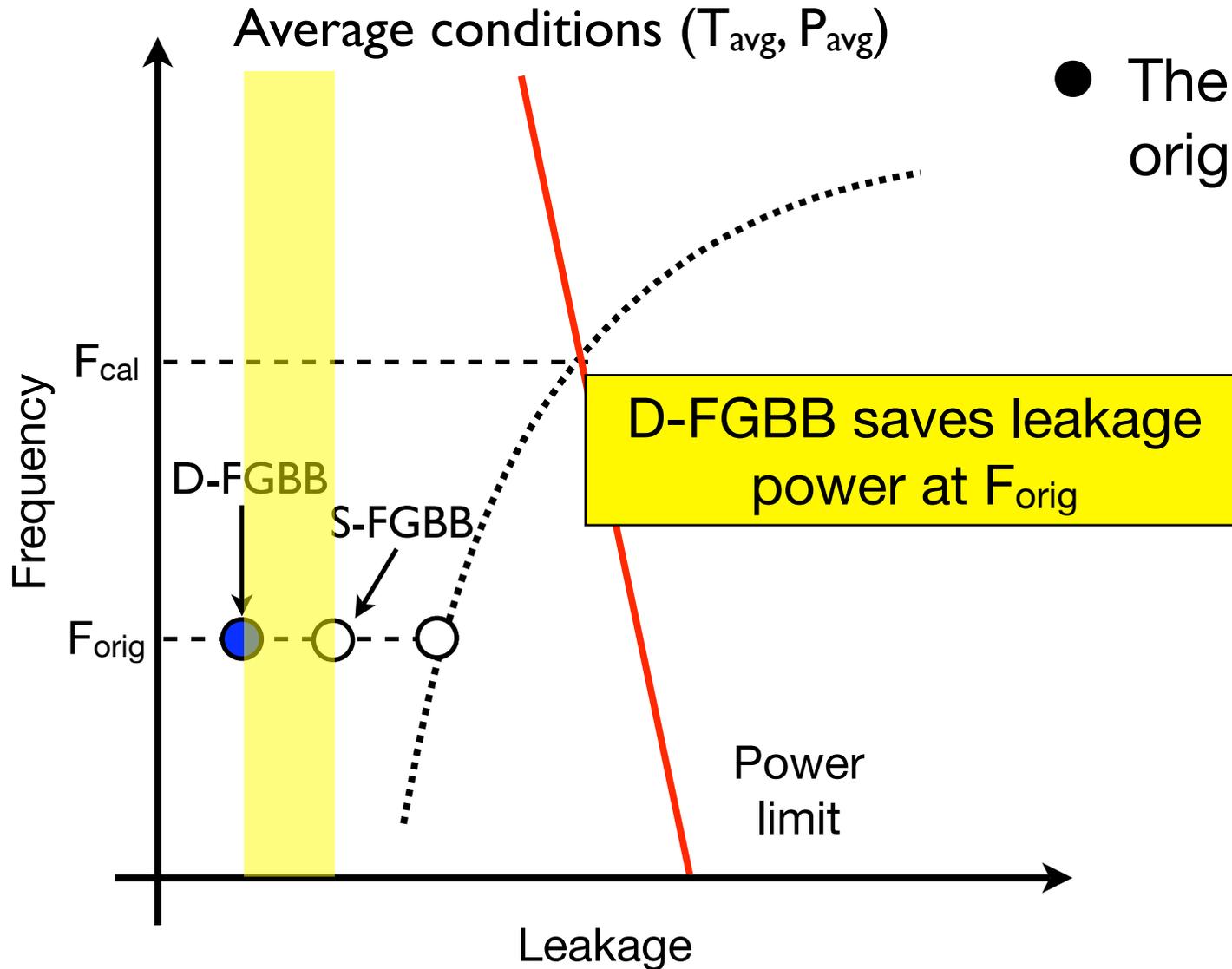
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# Evaluation infrastructure

- Process variation model - *VARIUS* [ASGI'07]
  - Generate  $V_{th}$  and  $L_{eff}$  variation maps for 200 chips
- SESC - cycle accurate microarchitectural simulator - execution time, dynamic power
  - Mix of SPECint and SPECfp benchmarks
- HotLeakage, SPICE model - leakage power
- Hotspot - temperature estimation

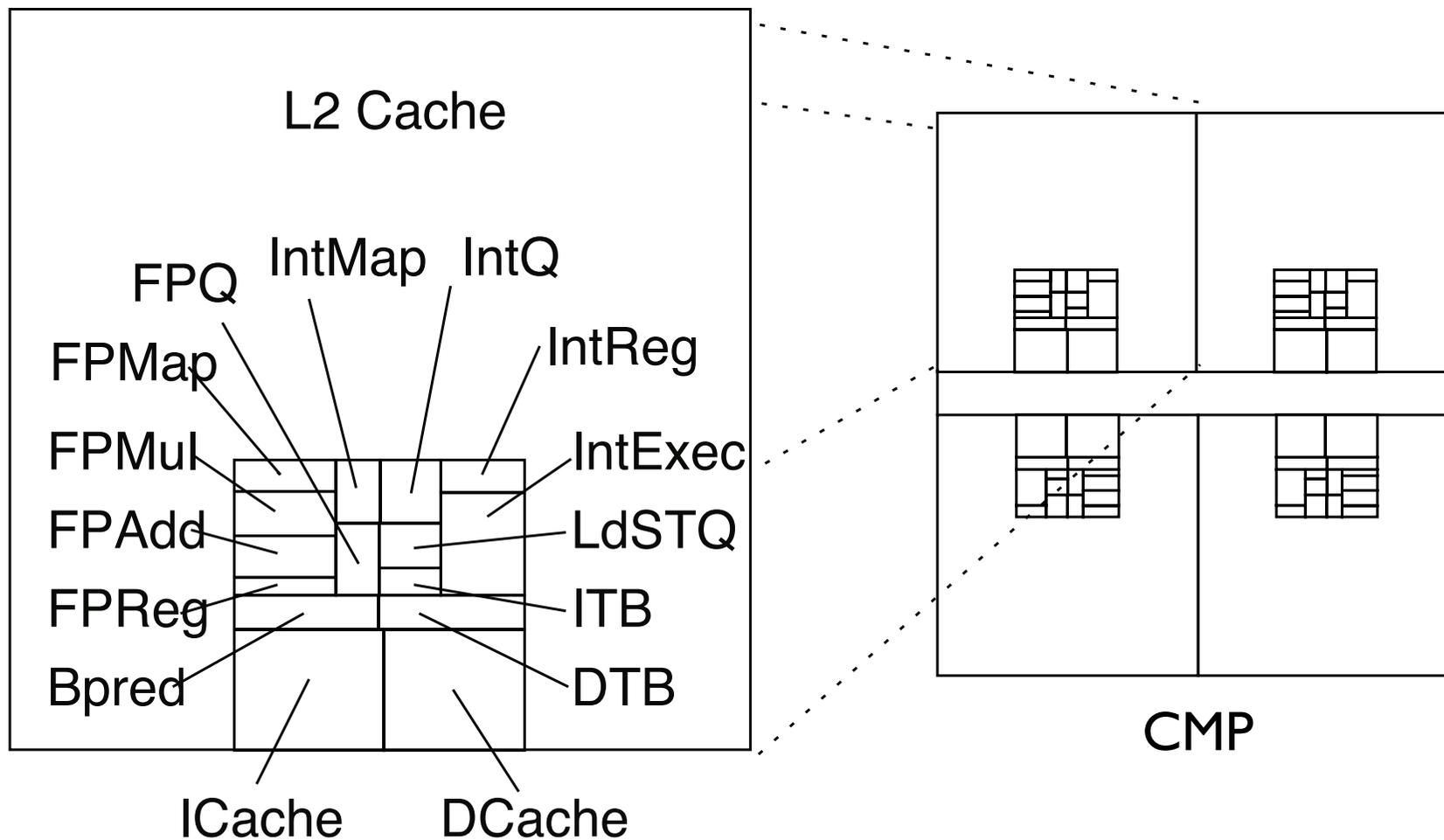


# Evaluation parameters

- 4-core CMP, based on Alpha 21364
- 45nm technology, 4GHz
- $V_{th}$  variation:  $\sigma_{V_{th}}/\mu_{V_{th}}=3-12\%$ ,  $\sigma_{sys}=\sigma_{rand}$
- $L_{eff}$  variation  $\sigma_{L_{eff}}= \sigma_{V_{th}}/2$
- $V_{dd}=1V$ ,  $V_{th0}=250mV$ ,  $V_{bb}= \pm 500mV$



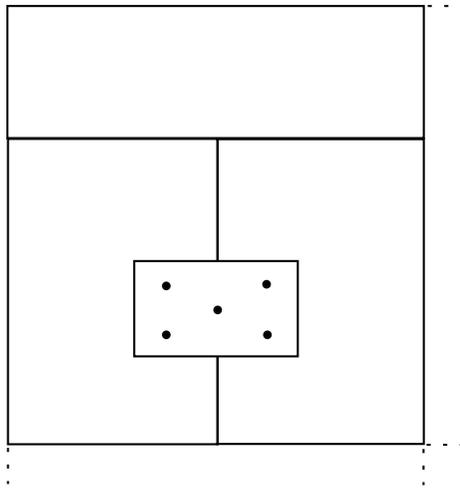
# CMP architecture



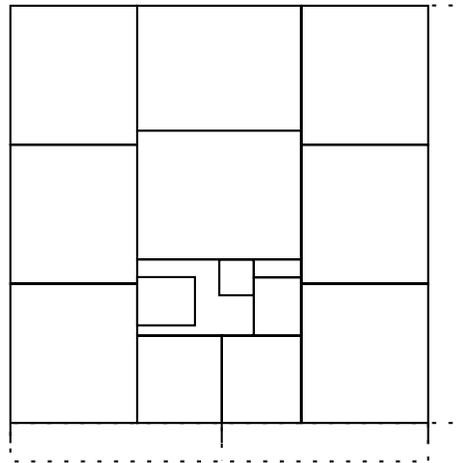


# Body bias granularity

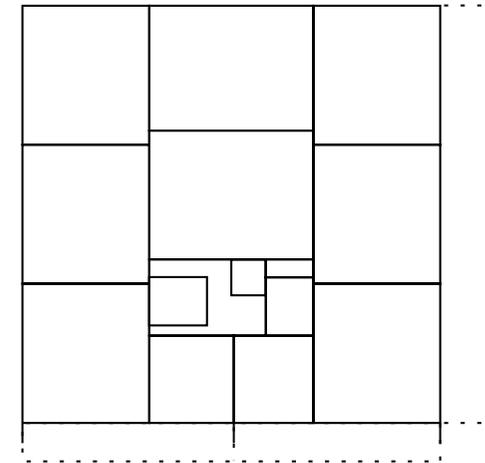
- We evaluate FGBB at different granularities
  - 1 - 144 BB cells per chip
  - Shapes and sizes follow functional units



FGBB16



FGBB64



FGBB144

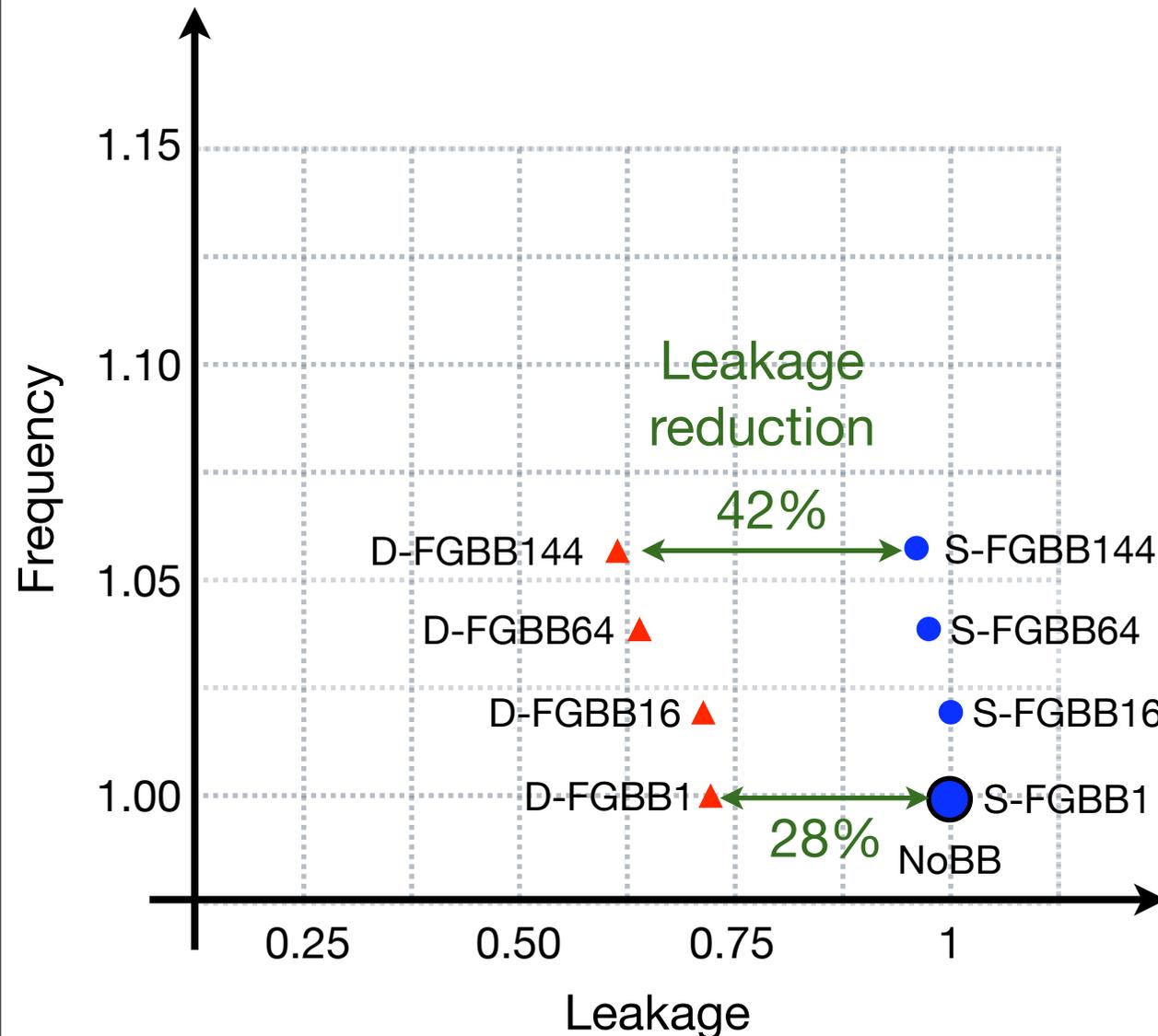


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# D-FGBB reduces leakage



- D-FGBB reduces leakage significantly
- More BB cells result in higher frequency and lower leakage

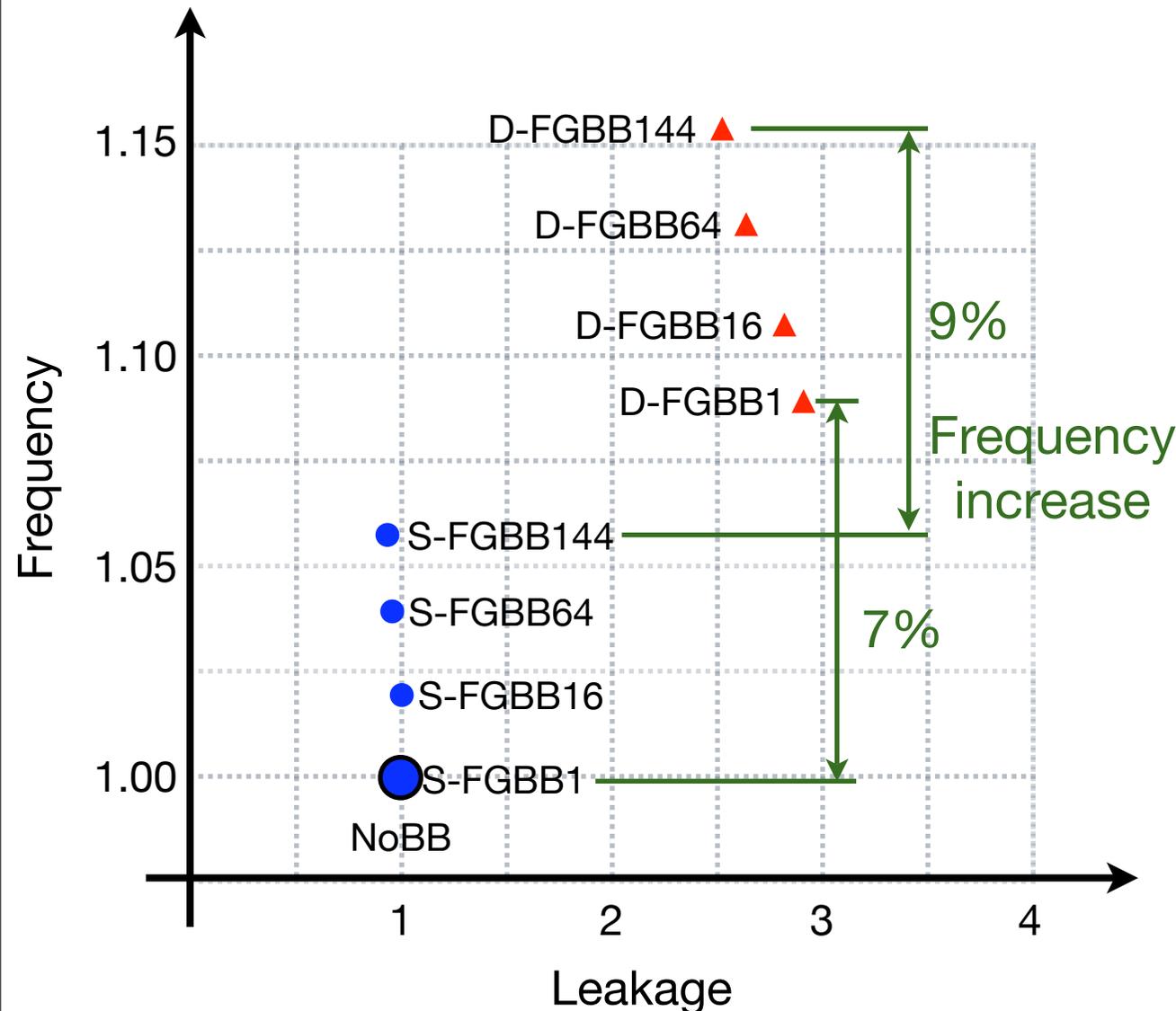


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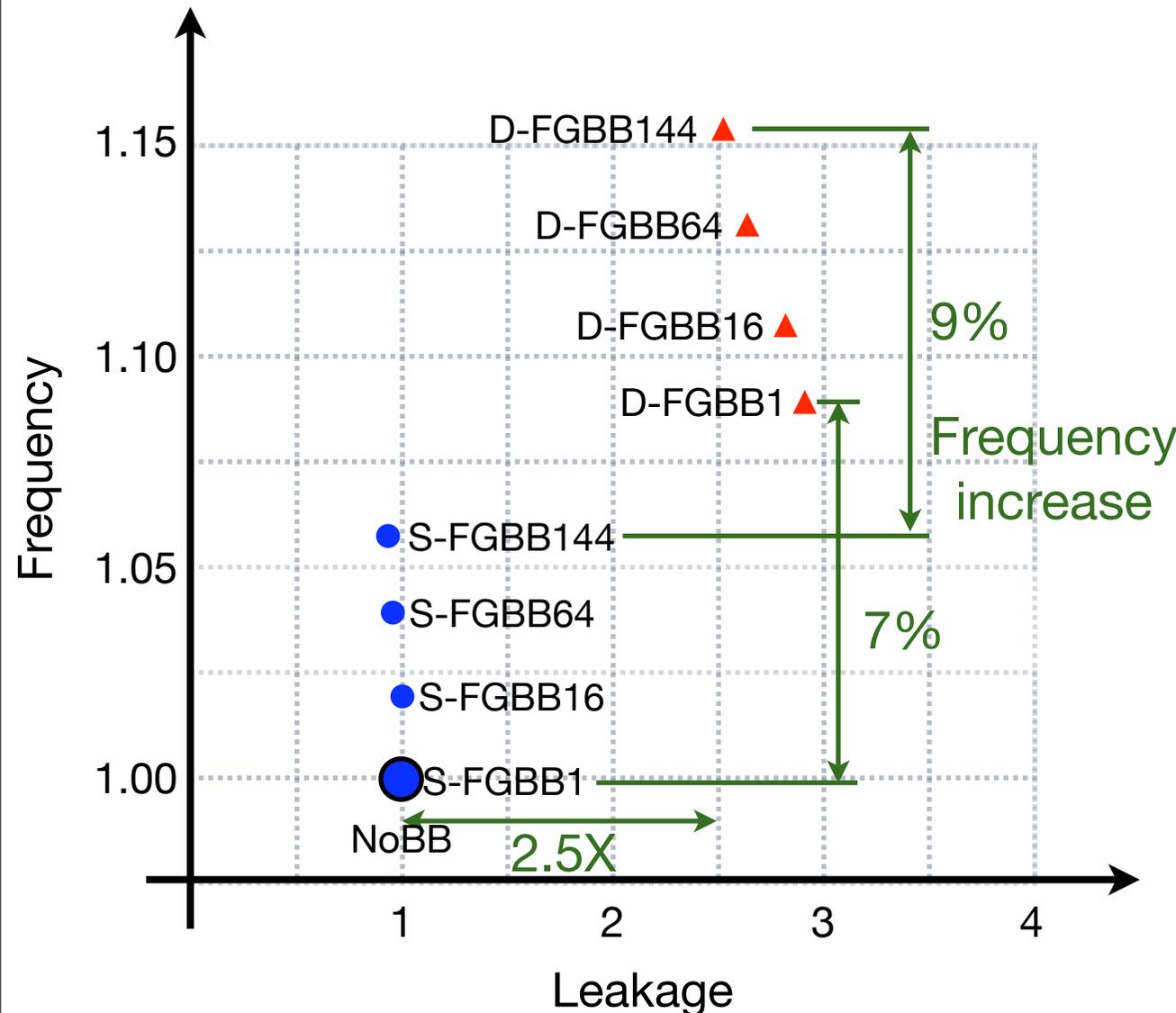
# D-FGGB improves frequency



- More BB cells result in a higher increase



# D-FGGB improves frequency



- More BB cells result in a higher increase
- Significant power cost, but still within the power budget

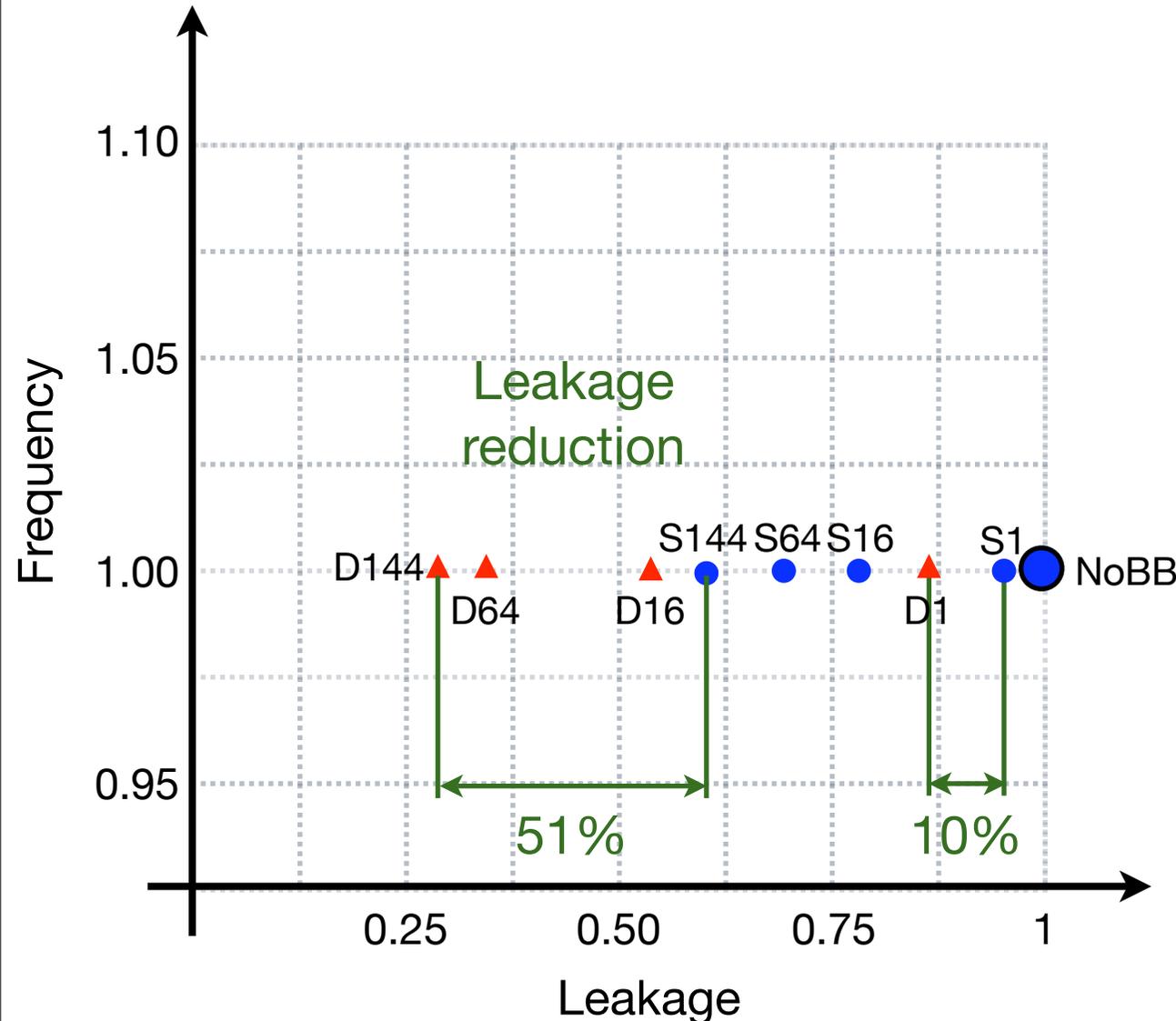


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# D-FGBB reduces leakage



- More BB cells result in higher savings



# Conclusions

- D-FGGB is more effective than S-FGGB at reducing WID variation:
  - 50% lower leakage
  - 10% higher frequency
  - because D-FGGB adapts to T variation
- D-FGGB can give architects an additional knob to tradeoff frequency/power





# More in the paper...

- Details about our variation model
- A solution for combining D-FGGB with DVFS
- Estimated overheads of D-FGGB
- More implementation details

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